

# An investigation of the screen grid tap

## A search for the hidden arguments.

By Rudolf Moers

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### APPENDICES

Mentioned screen grid taps  $x_{TURNS}$  in these appendices are the values from column 3 of table 7.

**For all anode characteristics in appendix A, C and E, the  $V_{gIk}$ -curves in the intervals  $0V \leq V_{ak} \leq 300V$  are measured with the  $\mu$ Tracer and the  $V_{gIk}$ -curves in the intervals  $300V \leq V_{ak} \leq 600V$  are extrapolated, so not measured.**

**By this 5 or 4 points of intersection on the load line are made with measured  $V_{gIk}$ -curves and the other 3 or 4 points of intersection on the load line are made with extrapolated  $V_{gIk}$ -curves.**

- A. Measured with the  $\mu$ Tracer and extrapolated anode characteristics of EL84 for several screen grid taps. Load line for EL84 goes through working point  $V_{ak,w} = 300V$ ,  $I_{a,w} = 40mA$  and  $V_{gIk,w} \approx -9.1V$ .
- B. Constructed dynamic transconductance characteristics of EL84 for several screen grid taps.
- C. Measured with the  $\mu$ Tracer and extrapolated anode characteristics of EL34 for several screen grid taps. Load line for EL34 goes through working point  $V_{ak,w} = 300V$ ,  $I_{a,w} = 80mA$  and  $V_{gIk,w} \approx -16.1V$ .
- D. Constructed dynamic transconductance characteristics of EL34 for several screen grid taps.
- E. Measured with the  $\mu$ Tracer and extrapolated anode characteristics of KT88 for several screen grid taps. Load line for KT88 goes through working point  $V_{ak,w} = 300V$ ,  $I_{a,w} = 80mA$  and  $V_{gIk,w} \approx -26.4V$ .
- F. Constructed dynamic transconductance characteristics of KT88 for several screen grid taps.

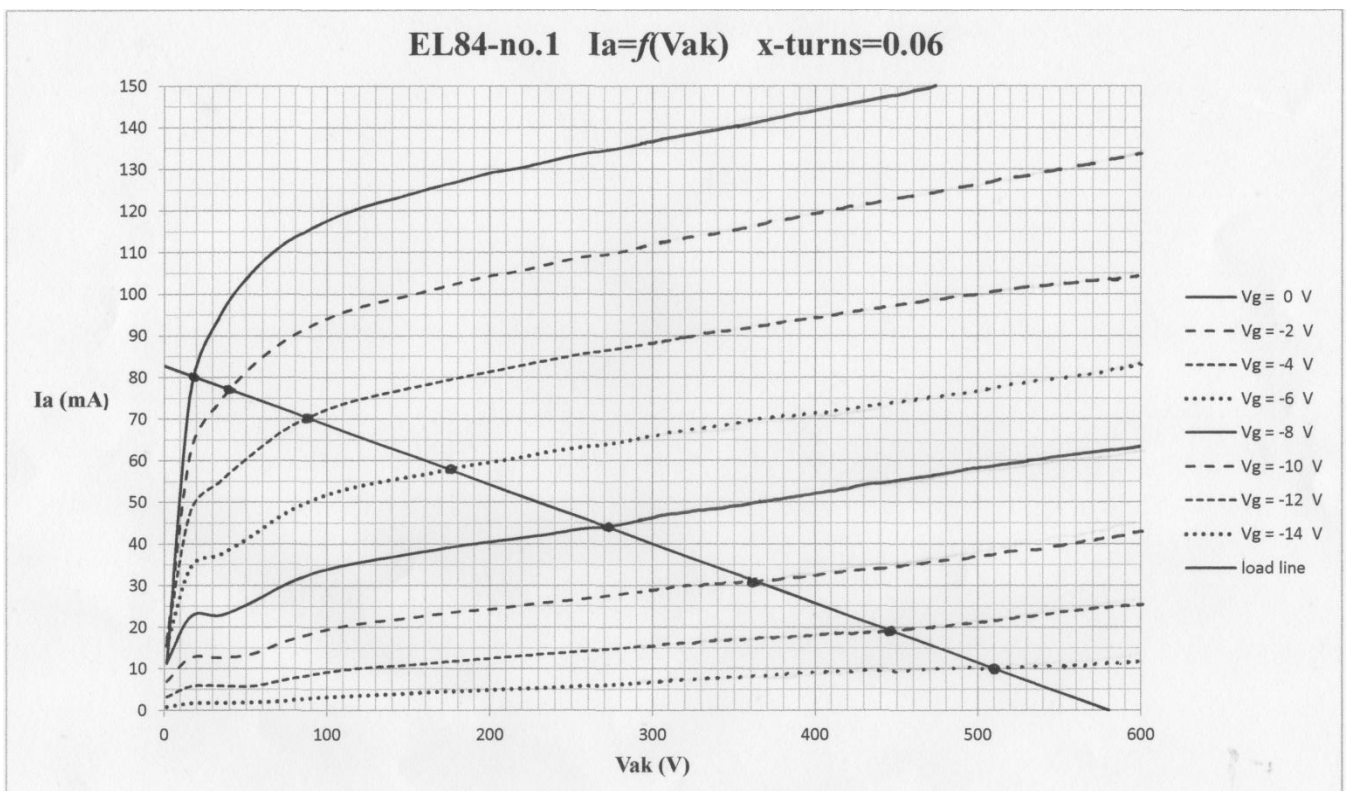
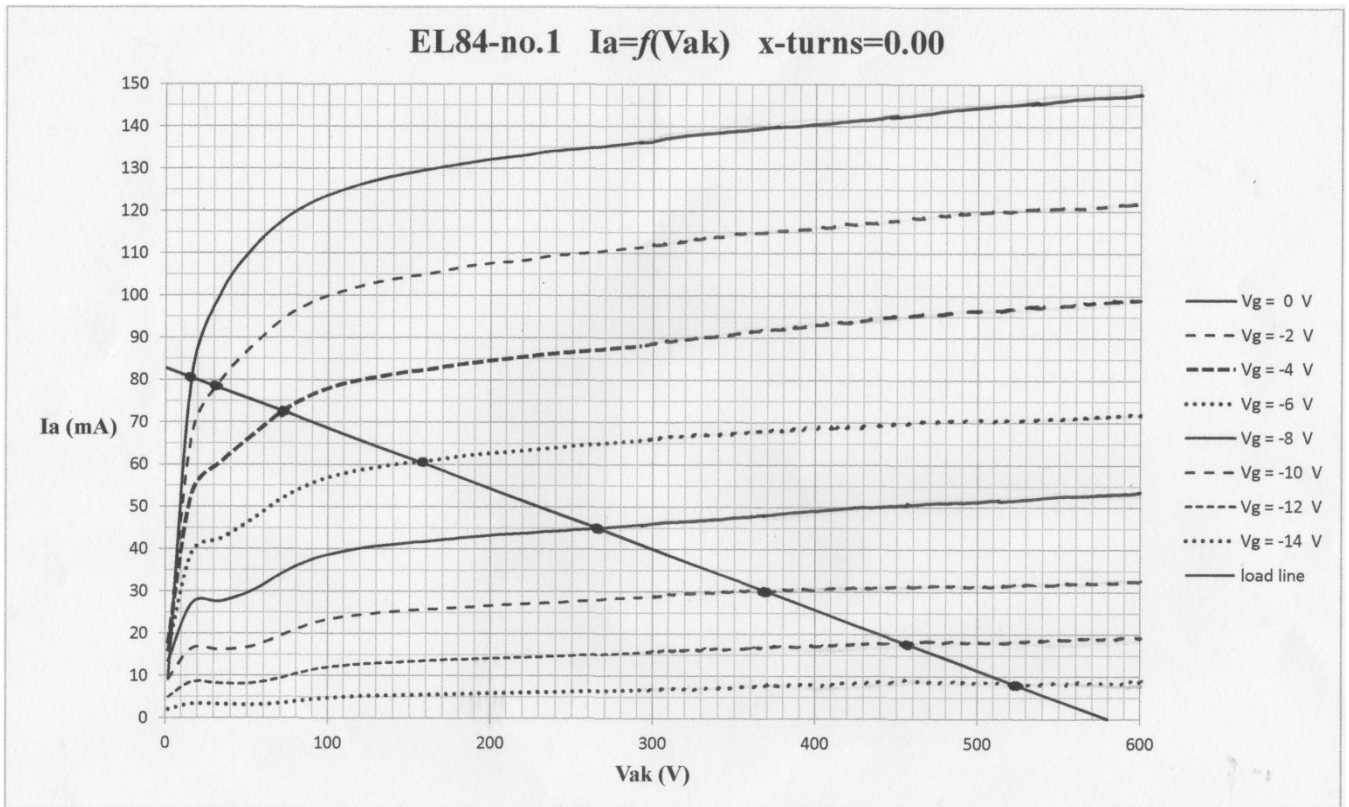
The constructed dynamic transconductances of appendix B are derived from the anode characteristics of appendix A (see the points of intersection of the  $V_{gIk}$ -curves with the load lines).

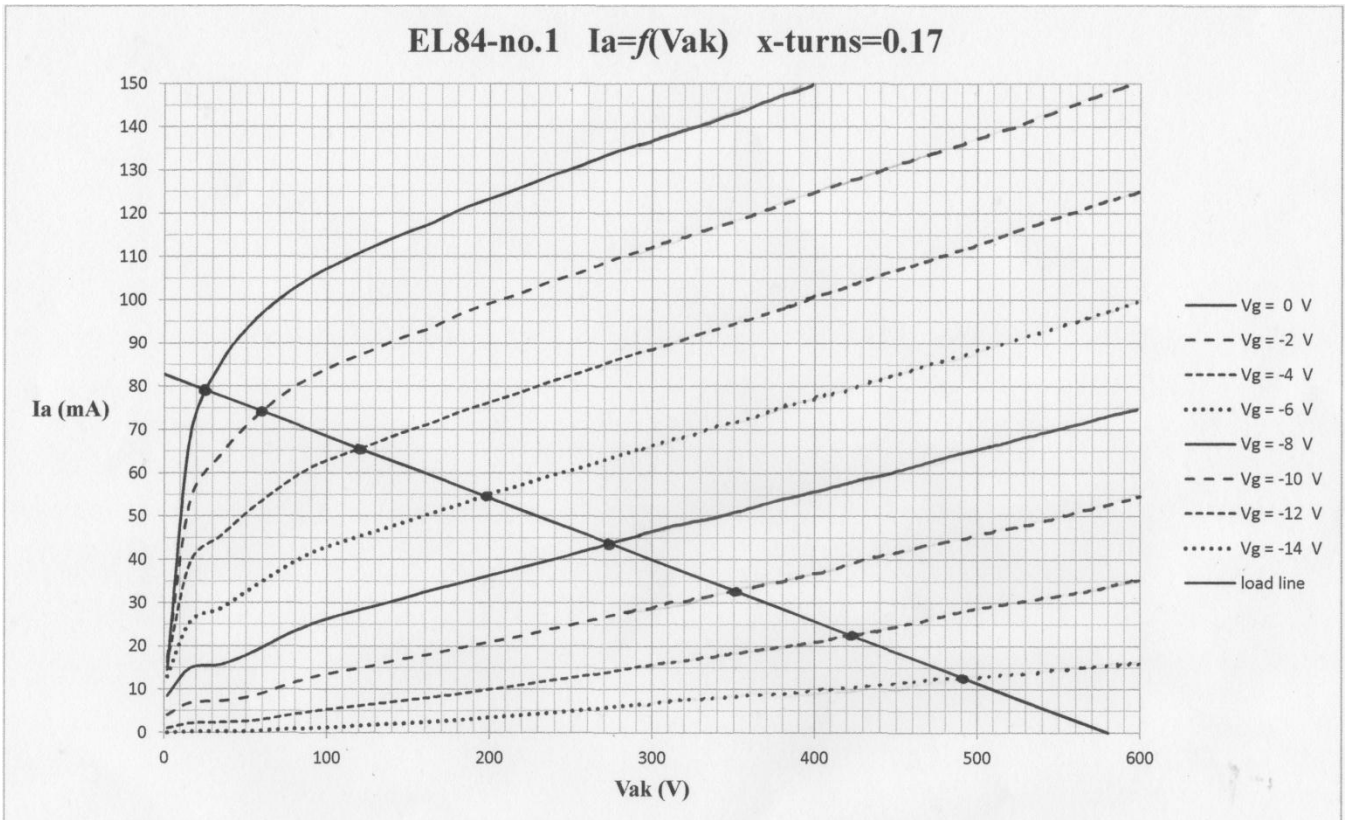
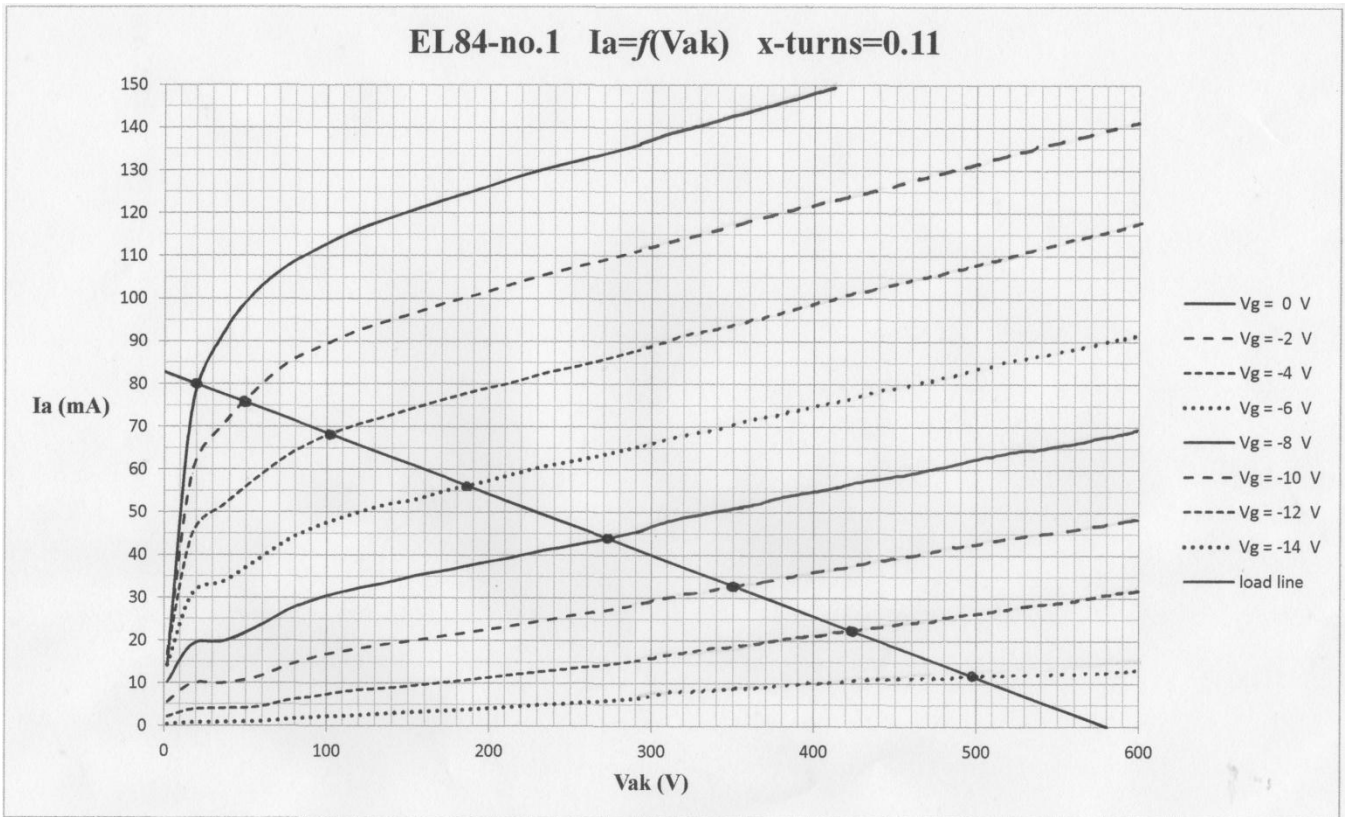
The constructed dynamic transconductances of appendix D are derived from the anode characteristics of appendix C (see the points of intersection of the  $V_{gIk}$ -curves with the load lines).

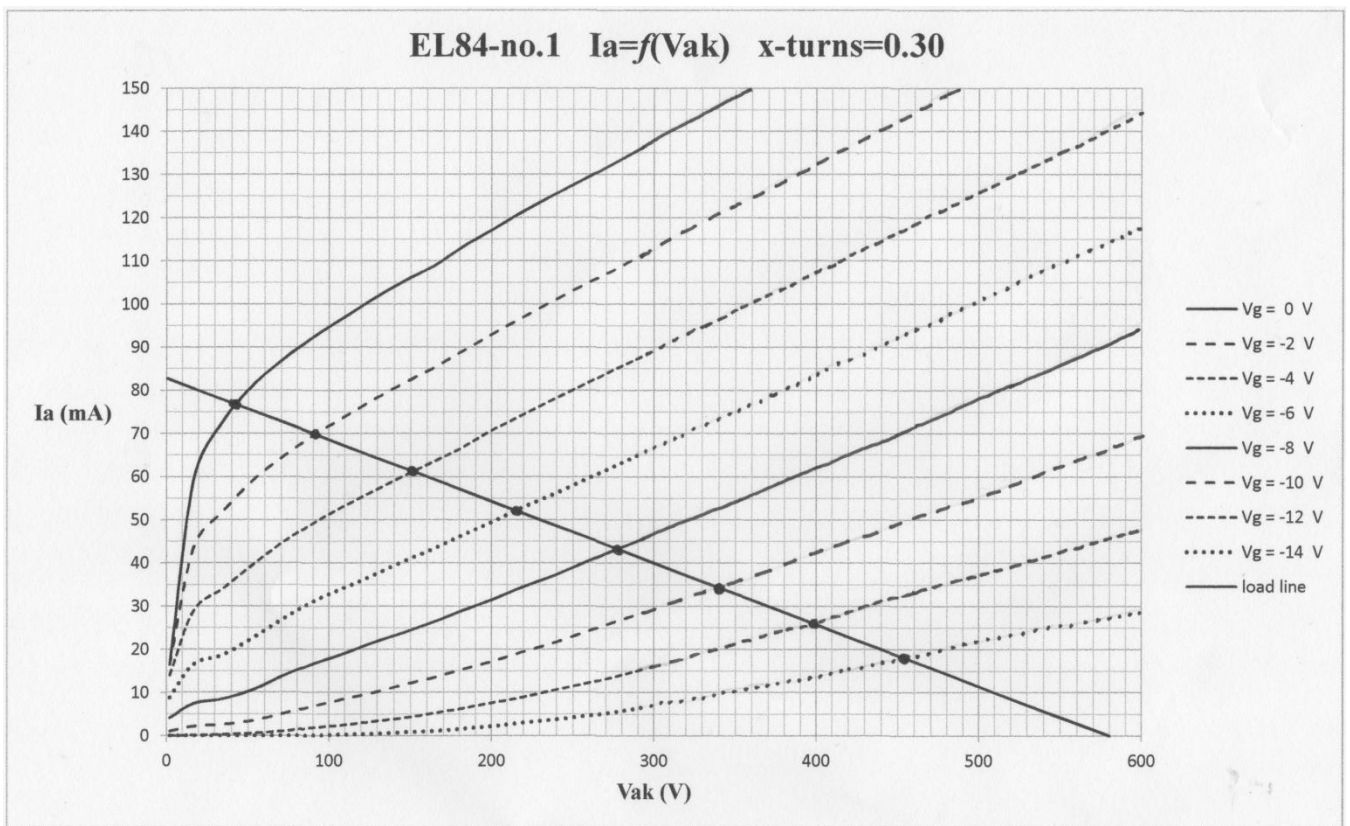
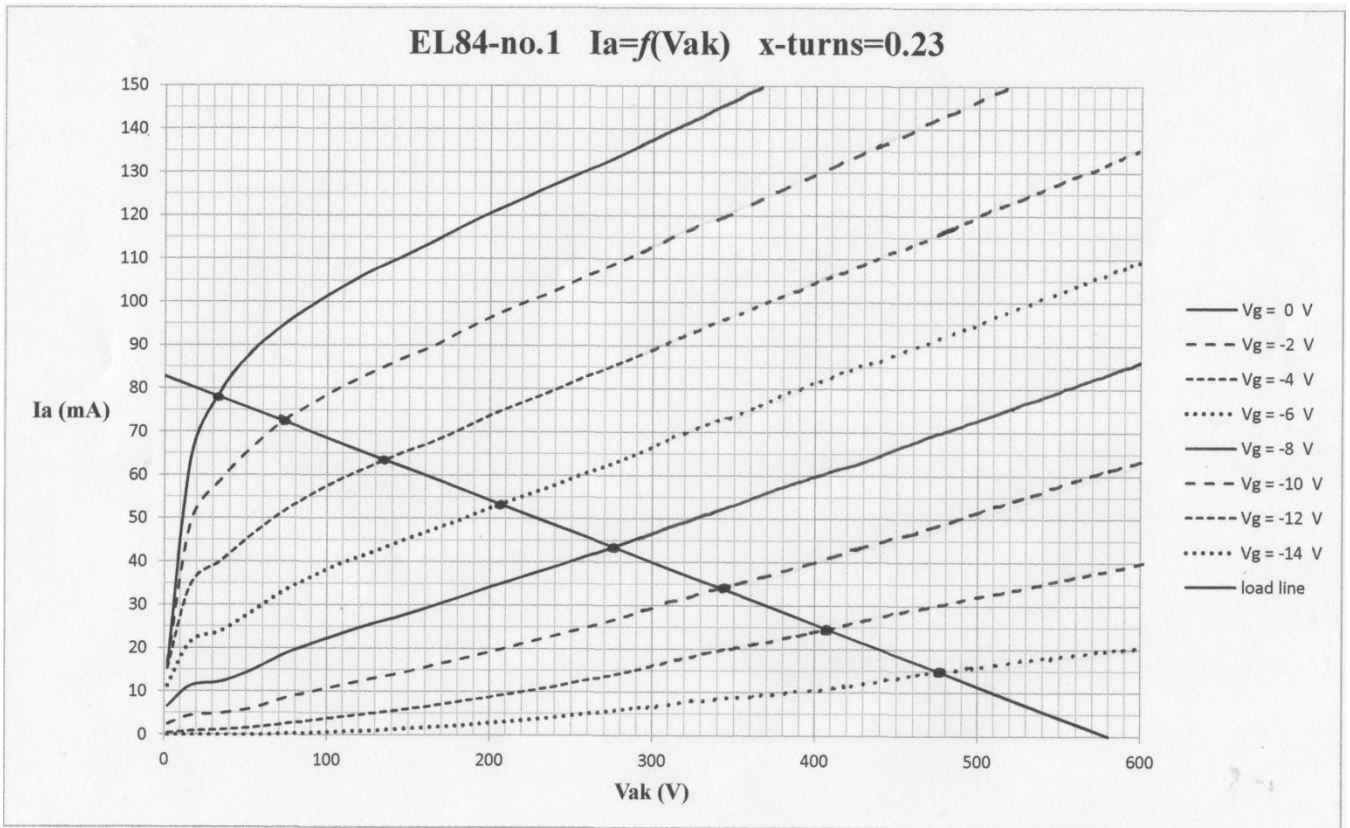
The constructed dynamic transconductances of appendix F are derived from the anode characteristics of appendix E (see the points of intersection of the  $V_{gIk}$ -curves with the load lines).

## APPENDIX A

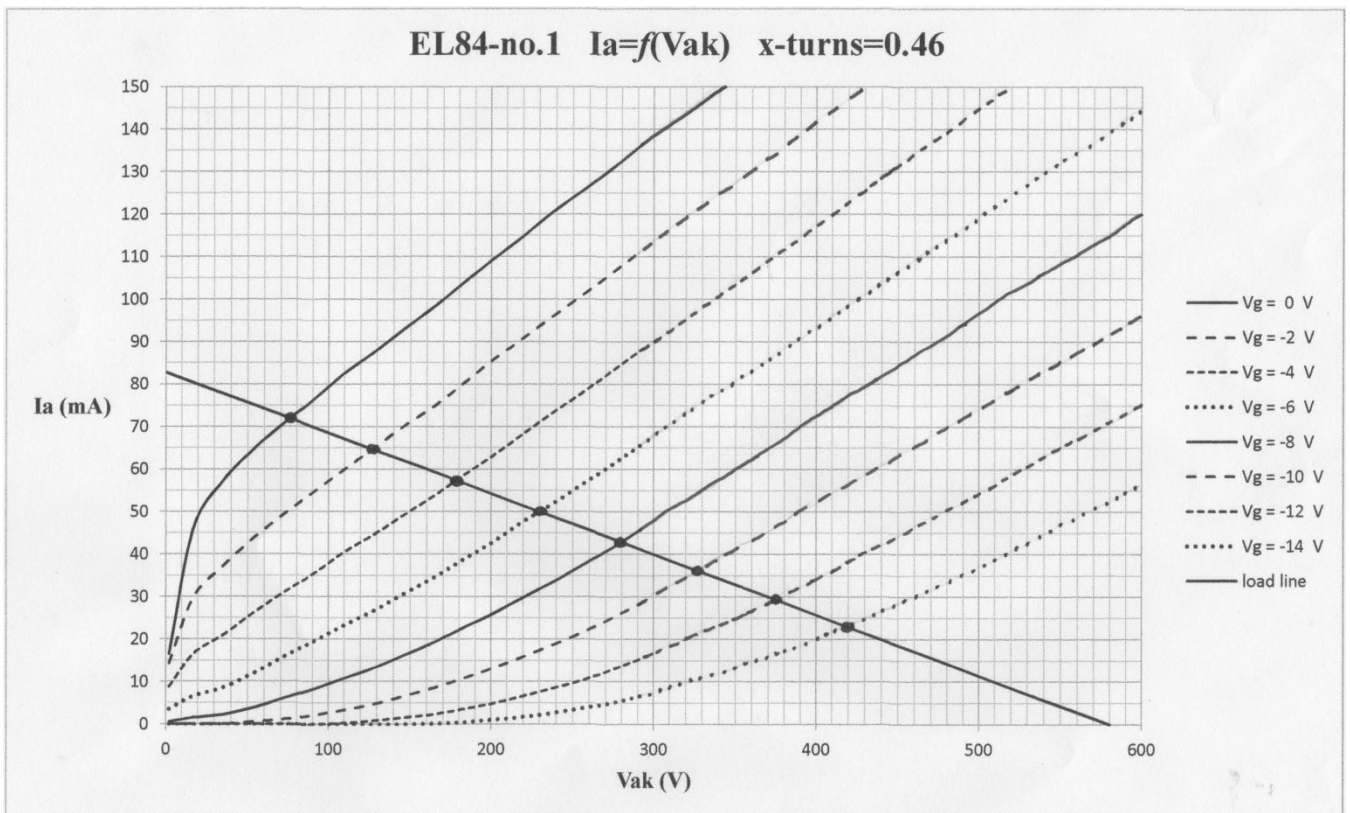
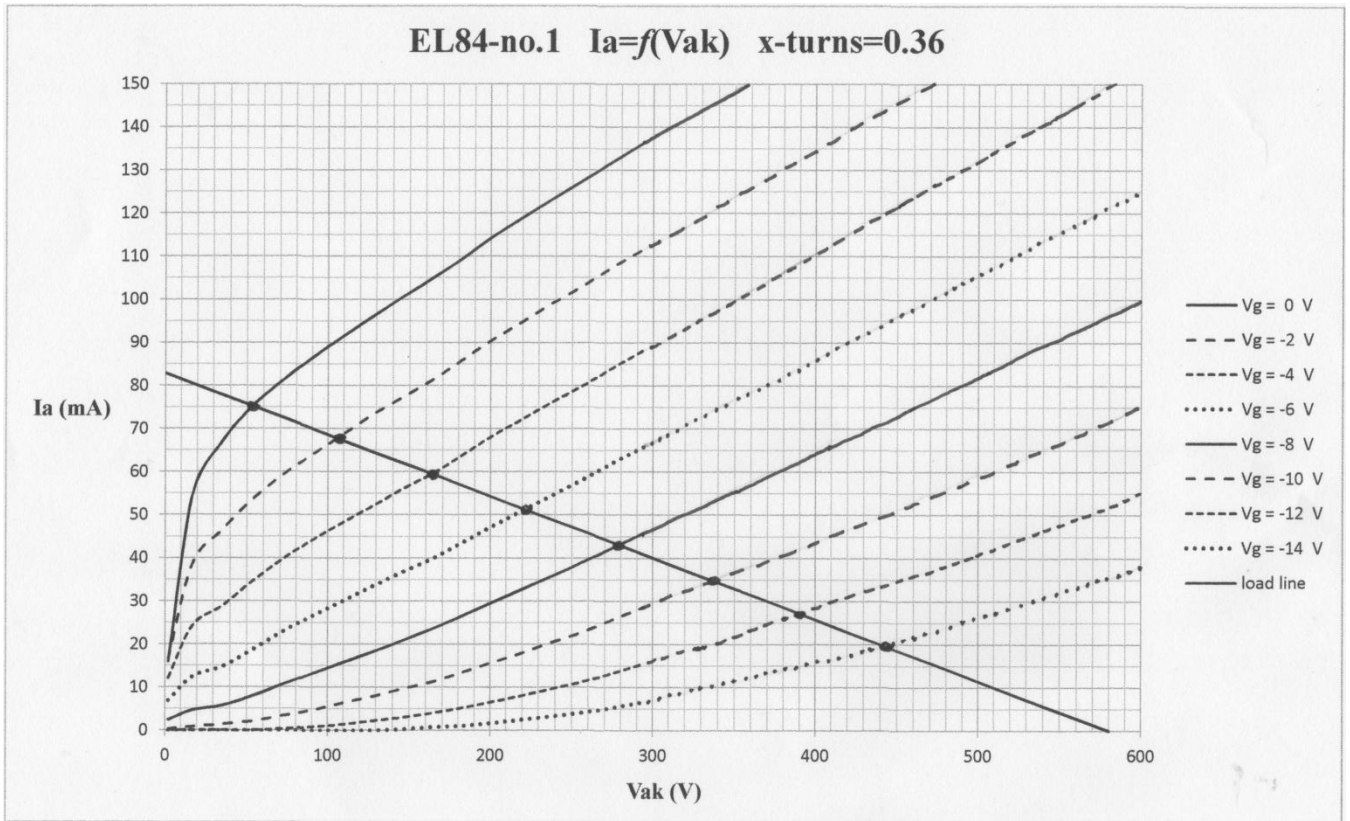
Measured with the  $\mu$ Tracer and extrapolated anode characteristics of EL84 for several screen grid taps. Load line for EL84 goes through working point  $V_{ak,w} = 300\text{V}$ ,  $I_{a,w} = 40\text{mA}$  and  $V_{gIk,w} \approx -9.1\text{V}$ .

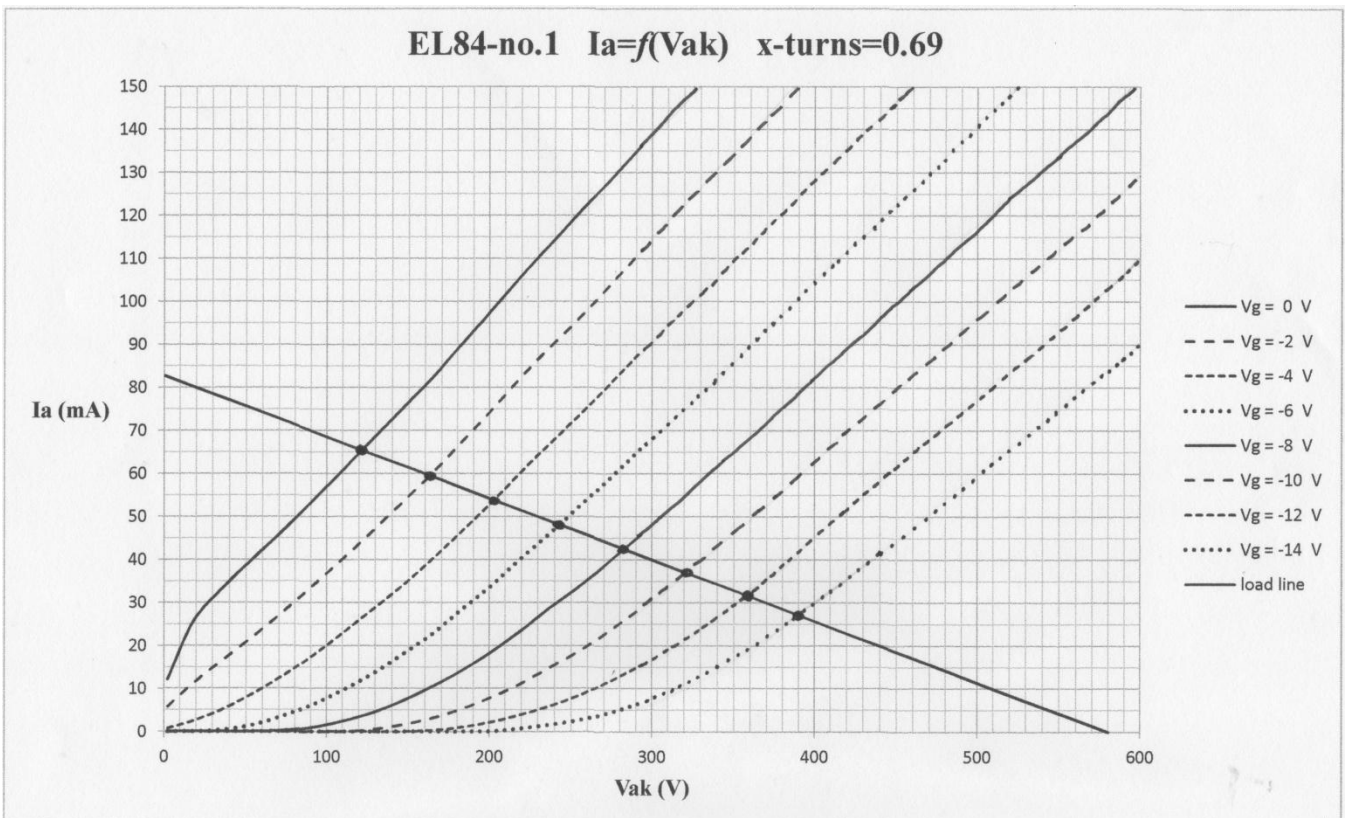
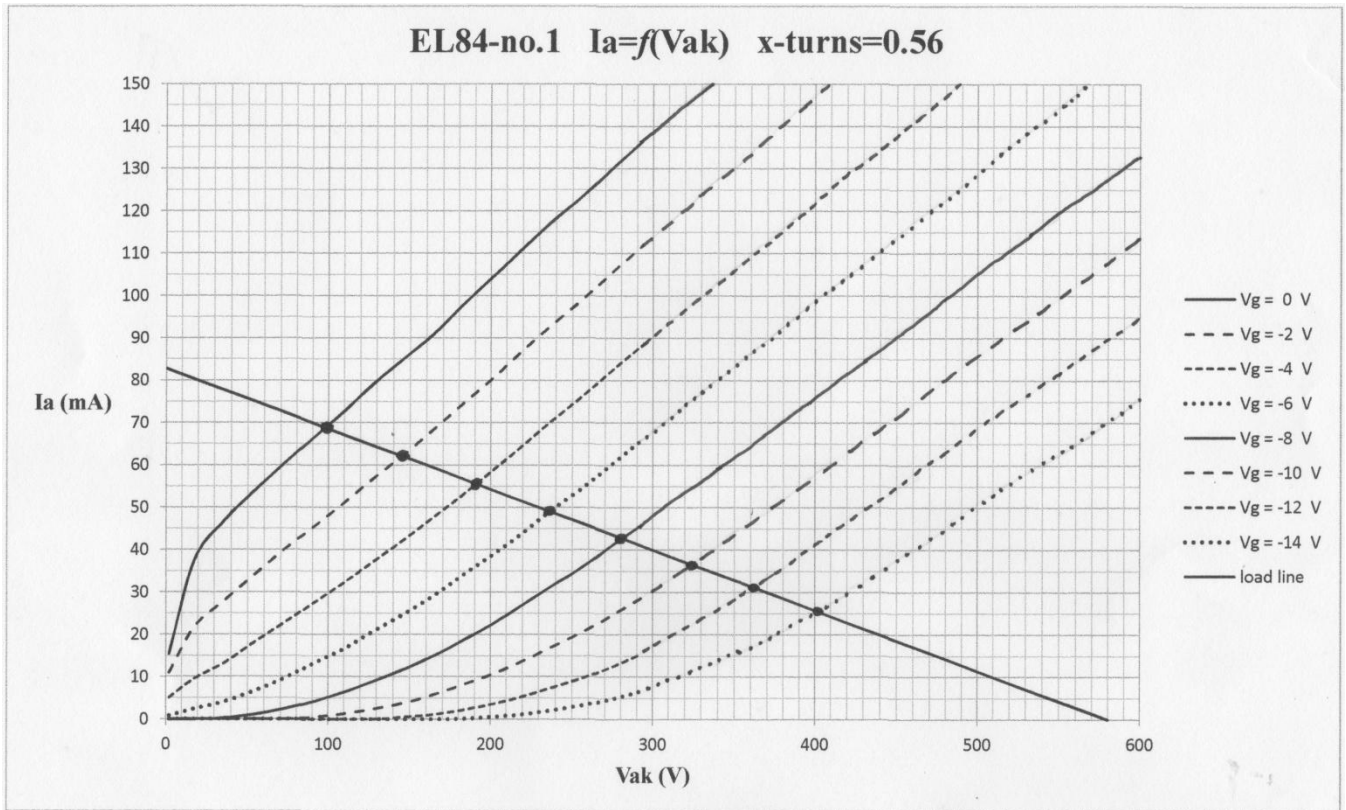


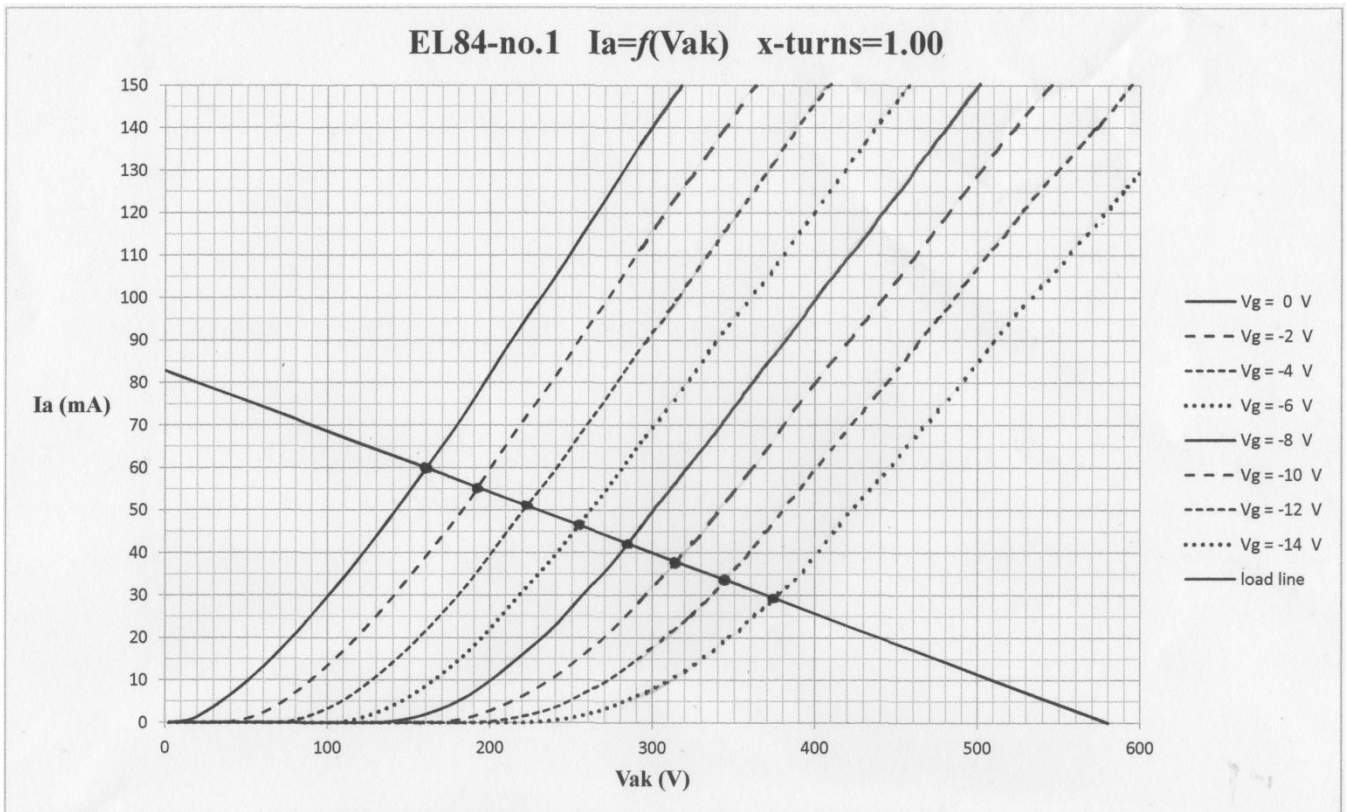






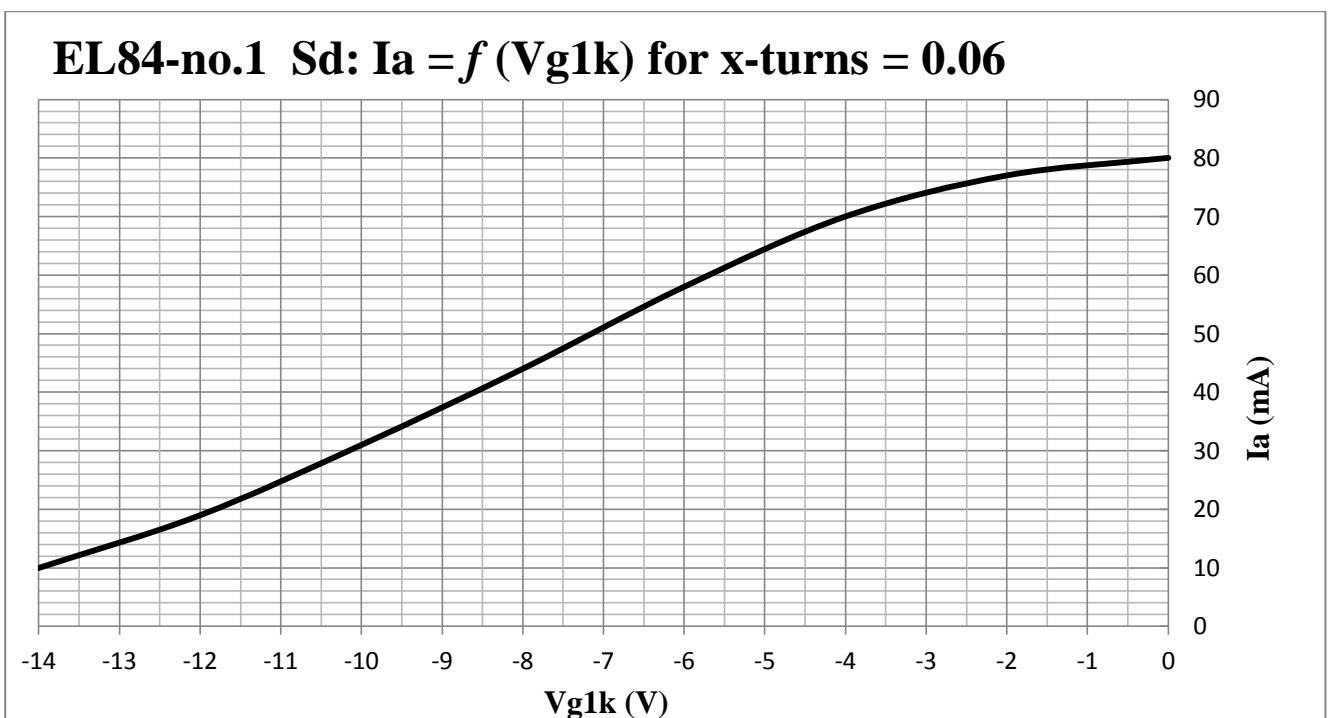
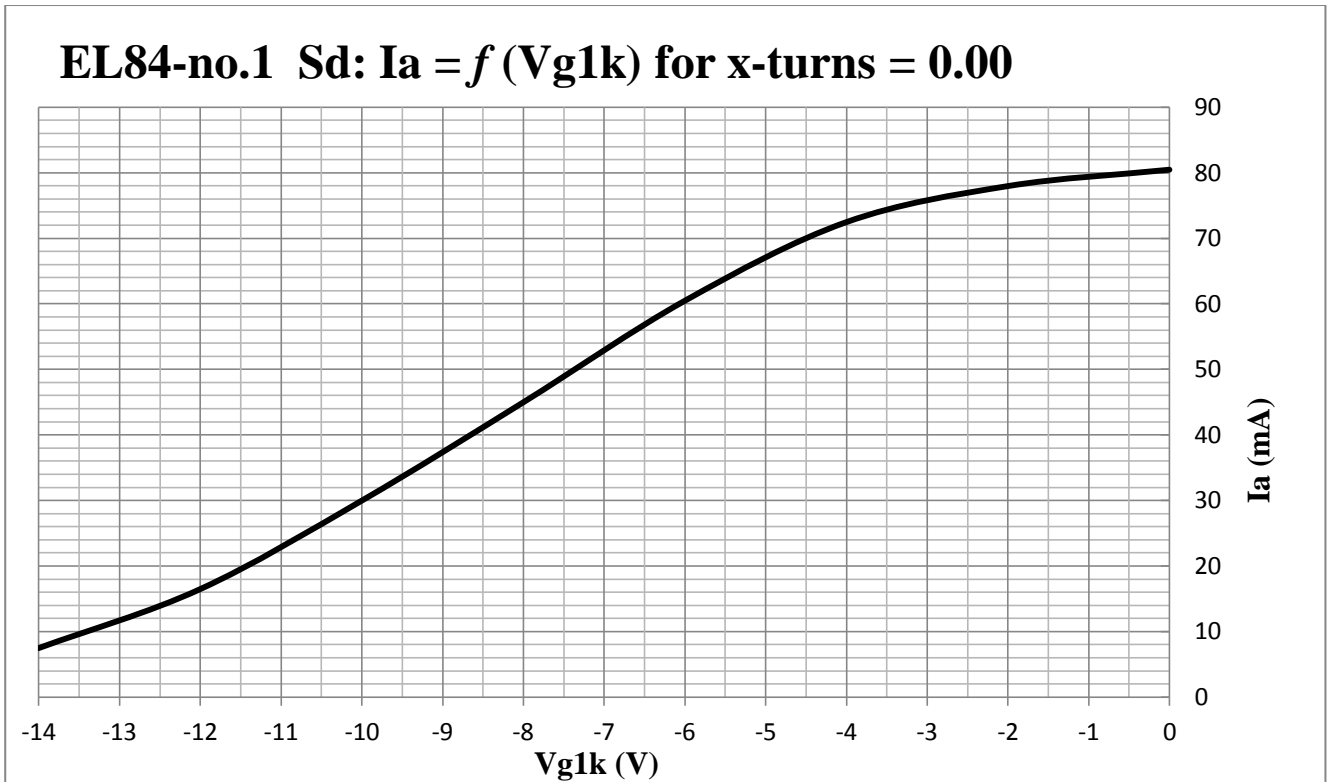




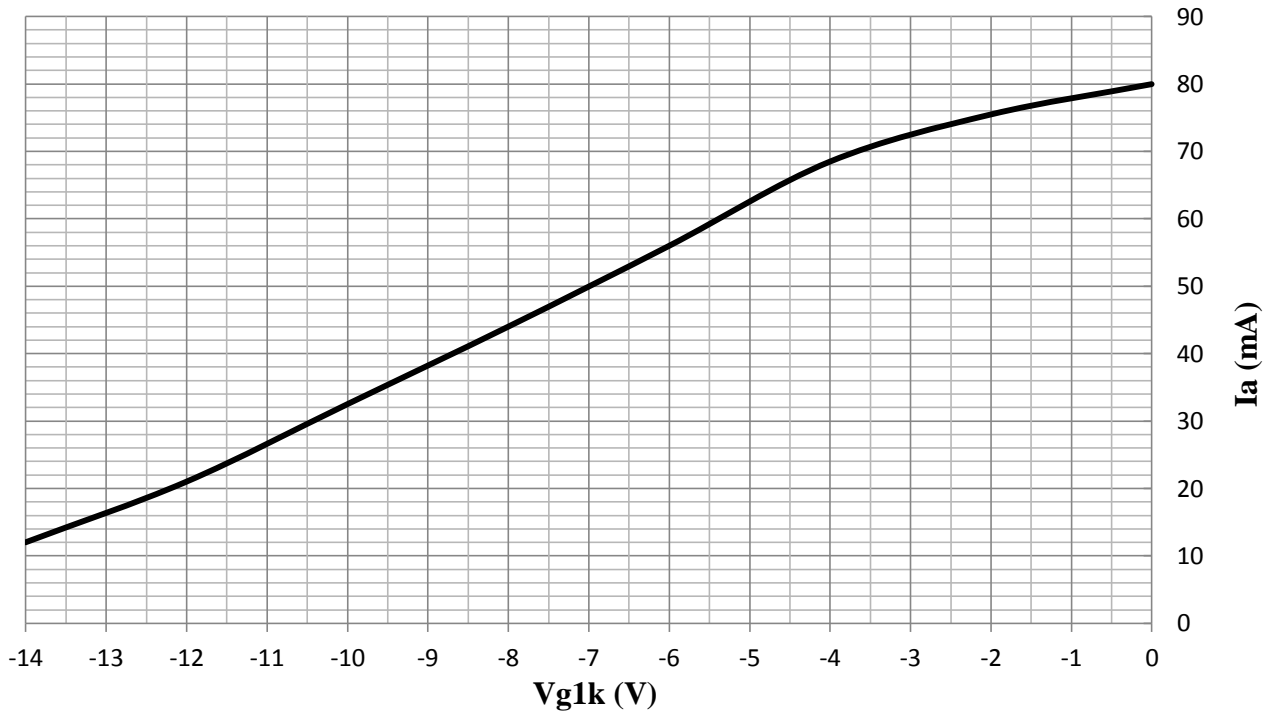
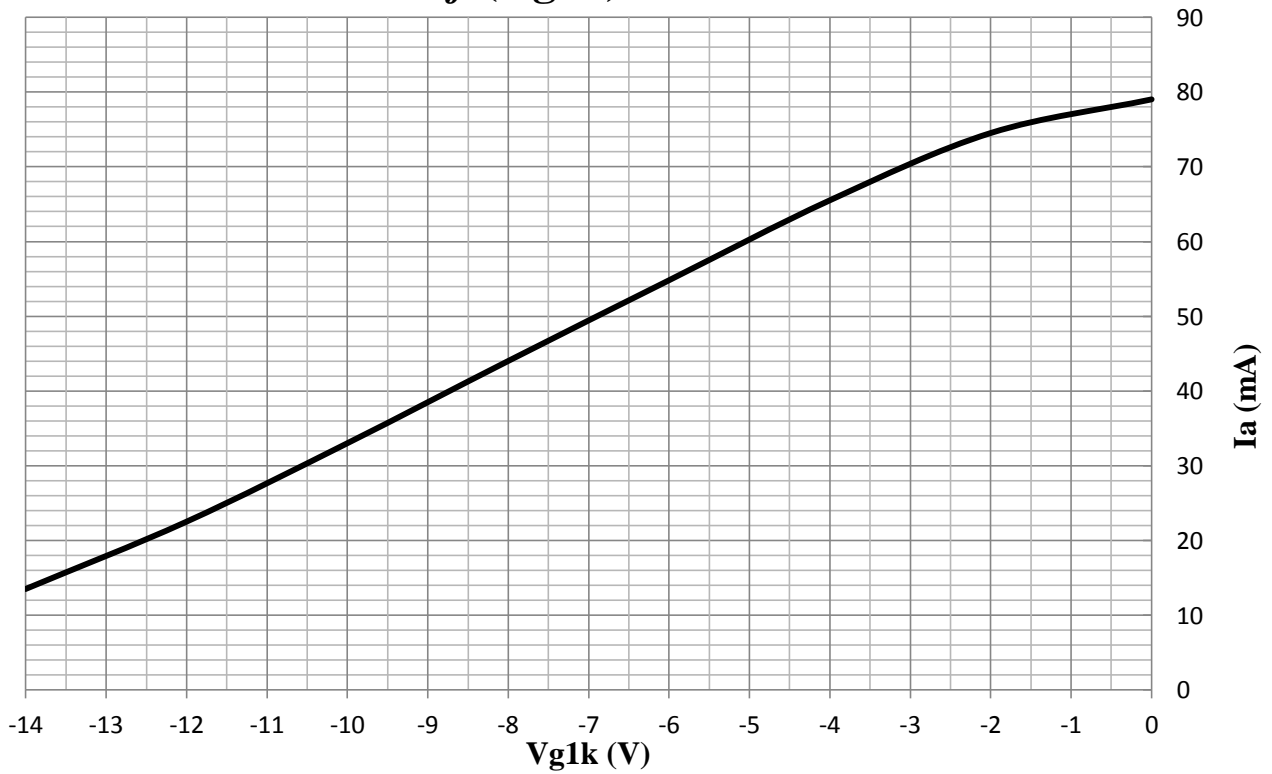


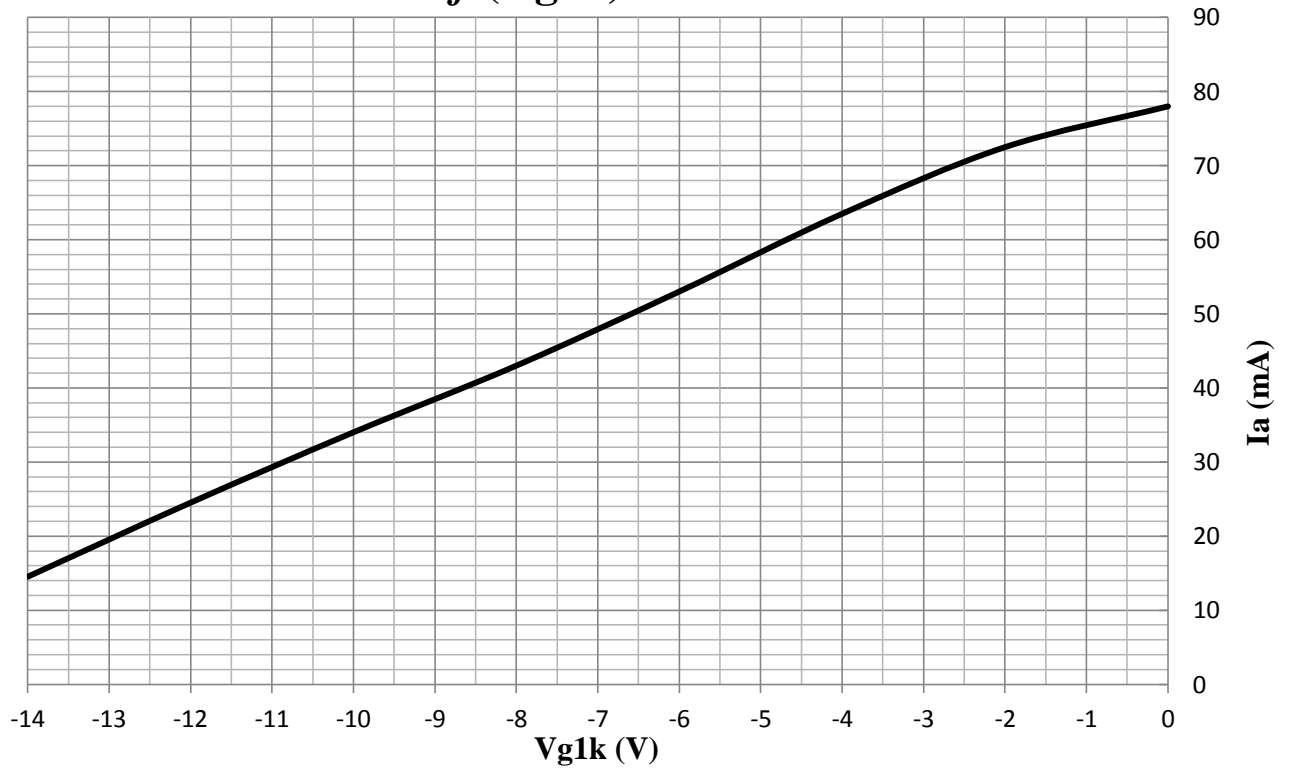
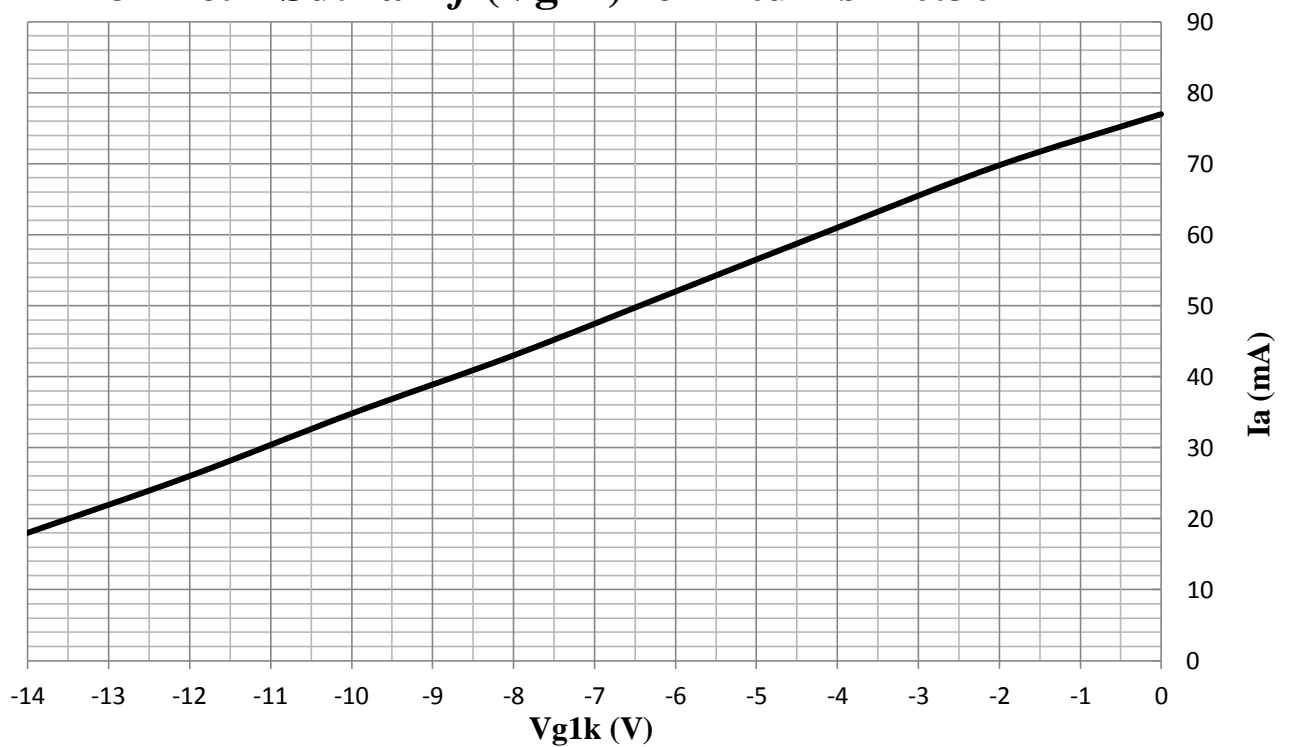
## APPENDIX B

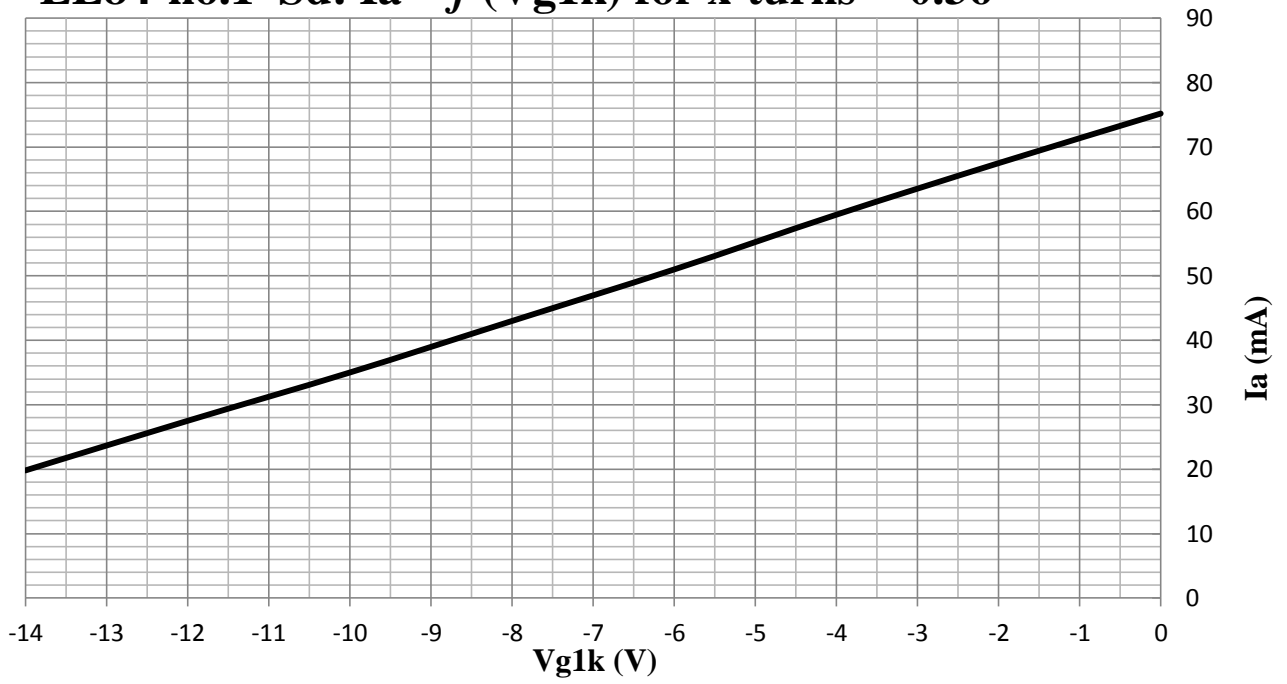
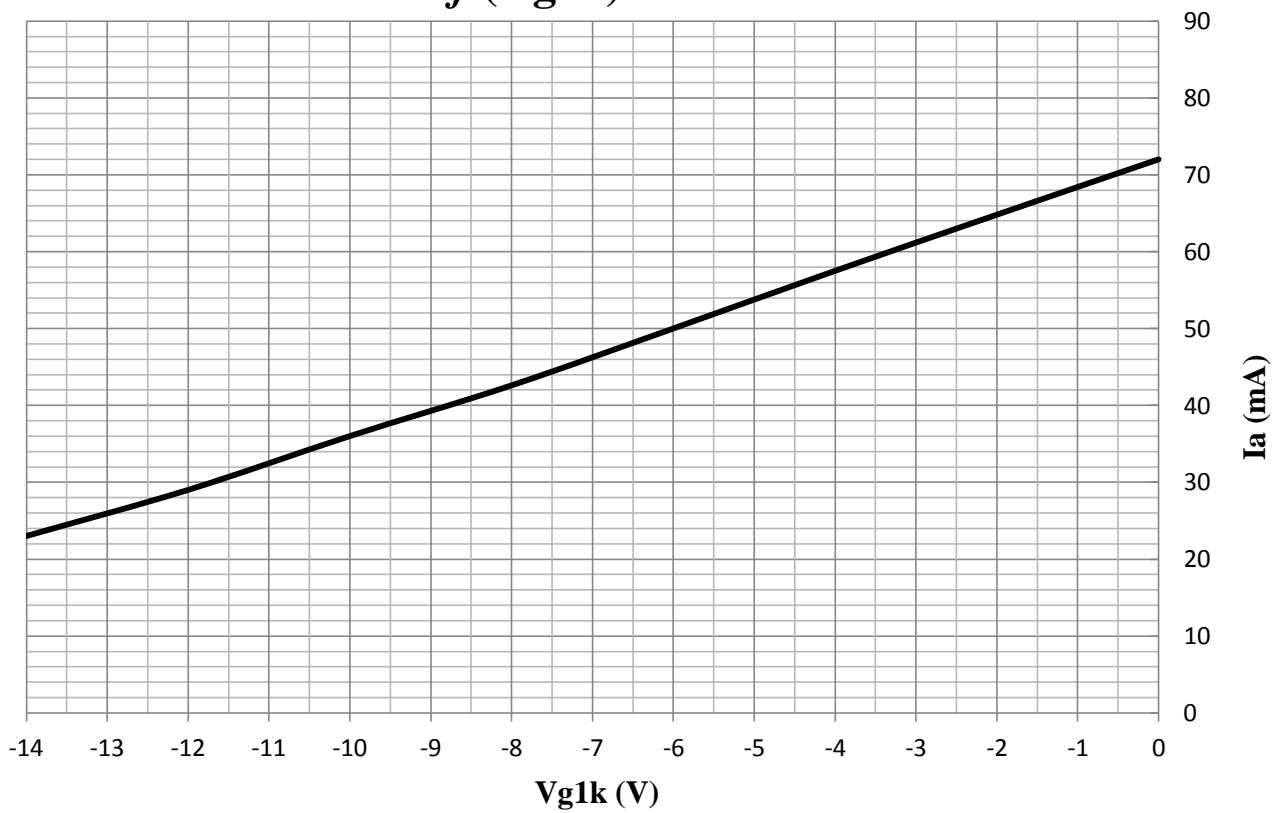
Constructed dynamic transconductance characteristics of EL84 for several screen grid taps.

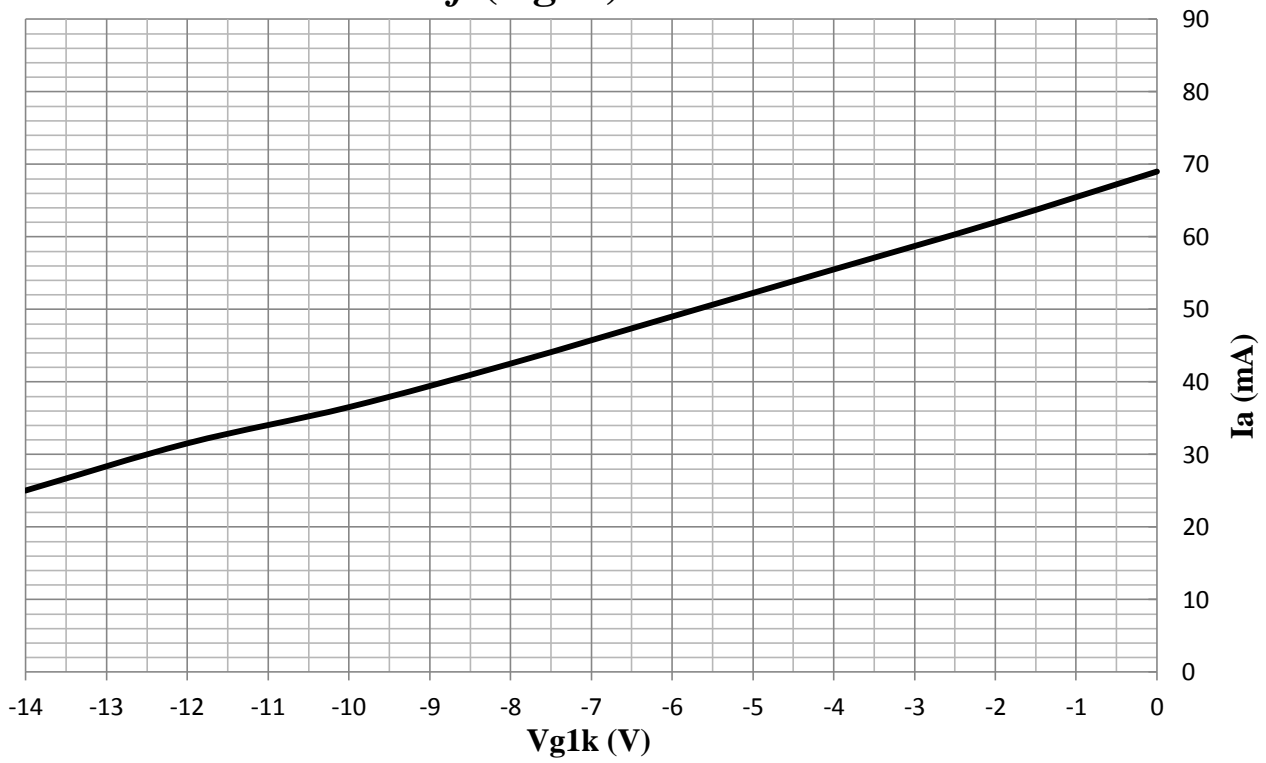
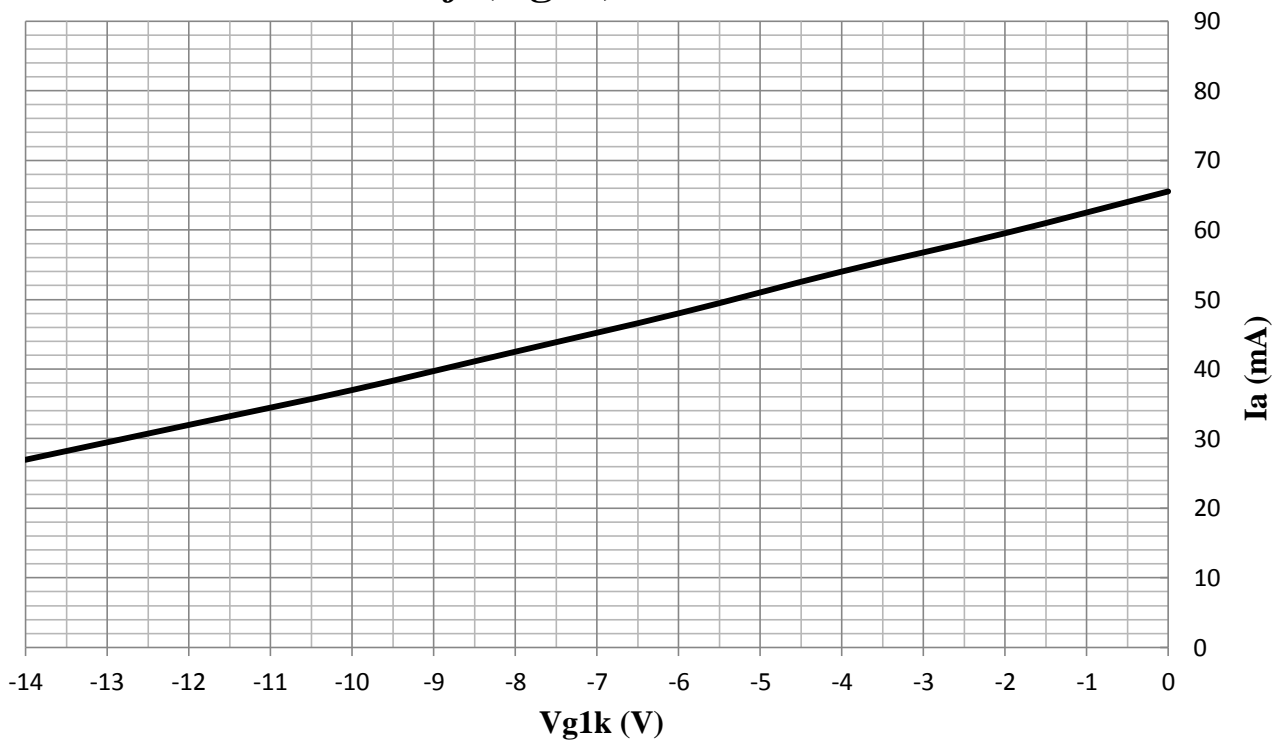


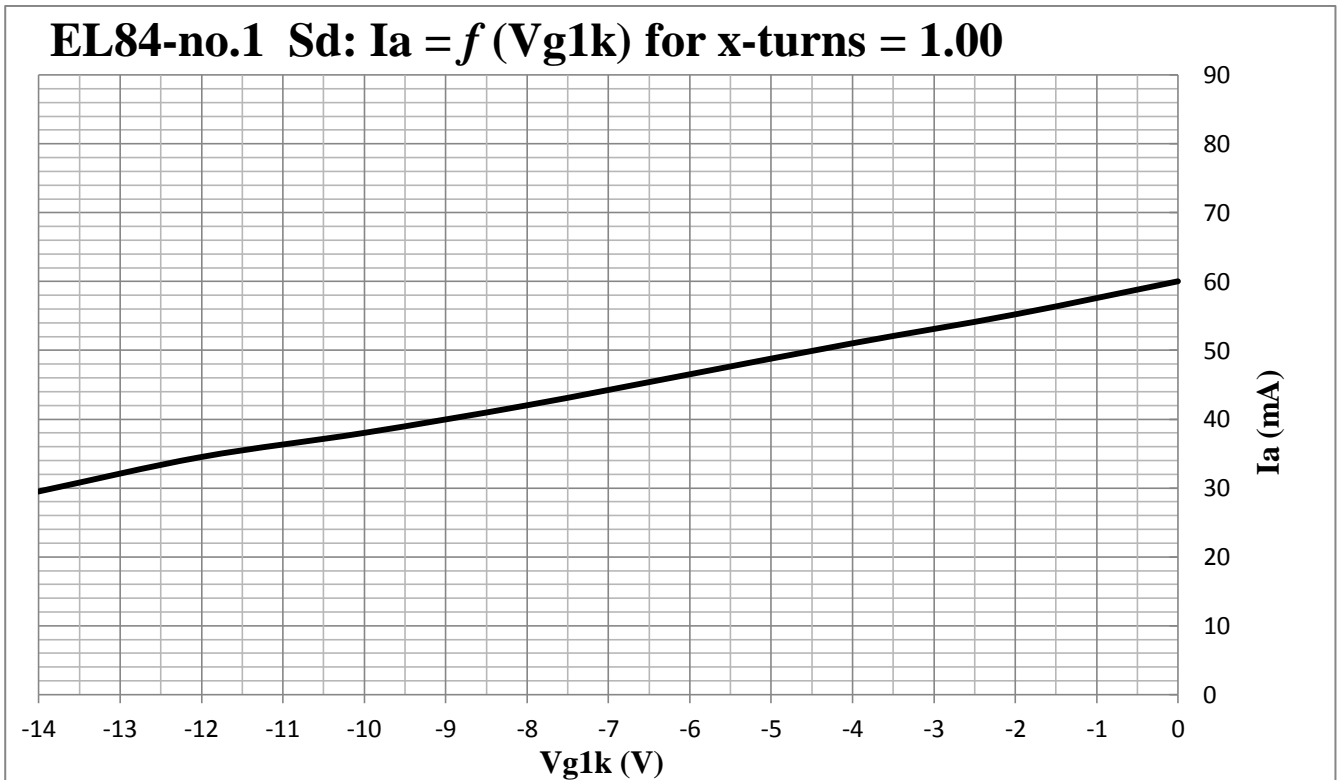


**EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.11****EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.17**

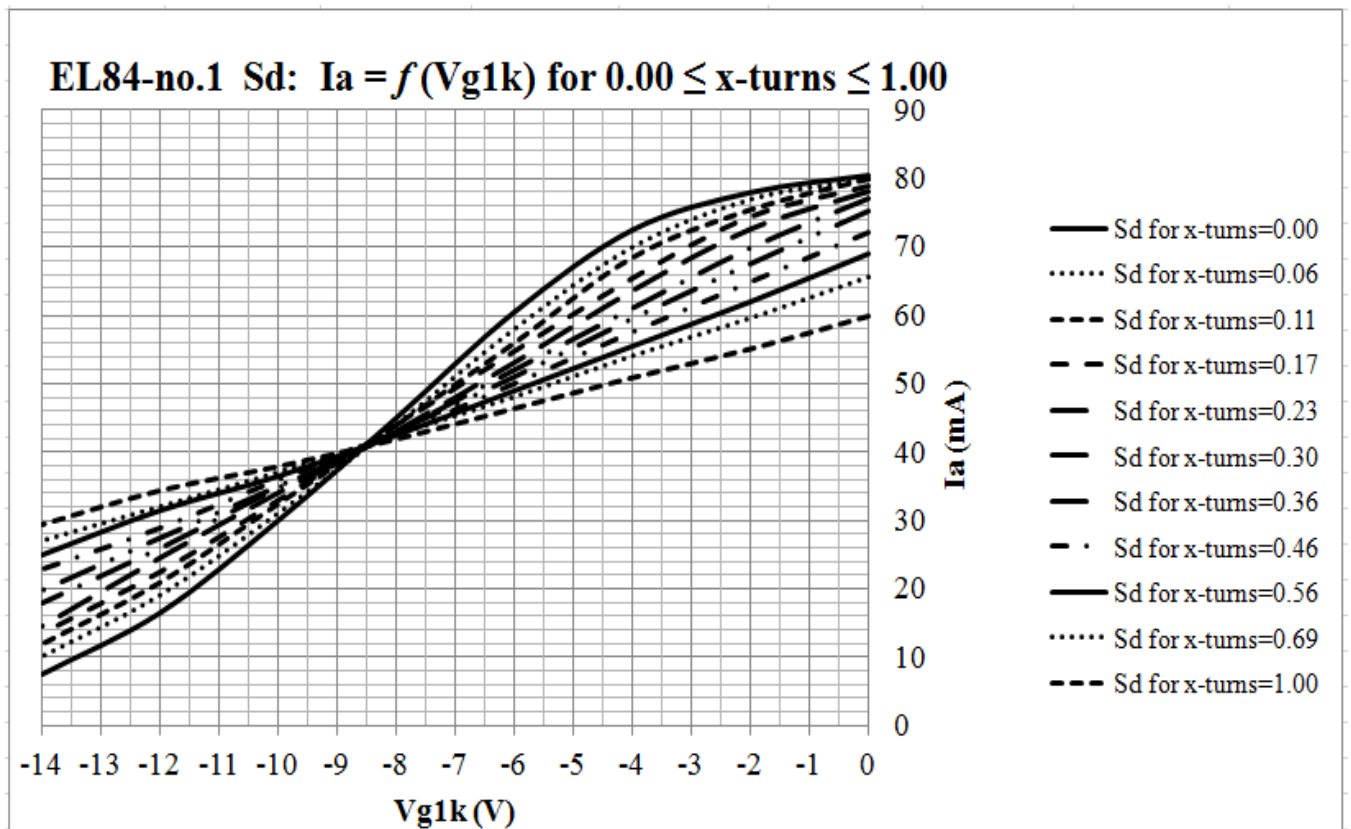
**EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.23****EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.30**

**EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.36****EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.46**

**EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.56****EL84-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.69**



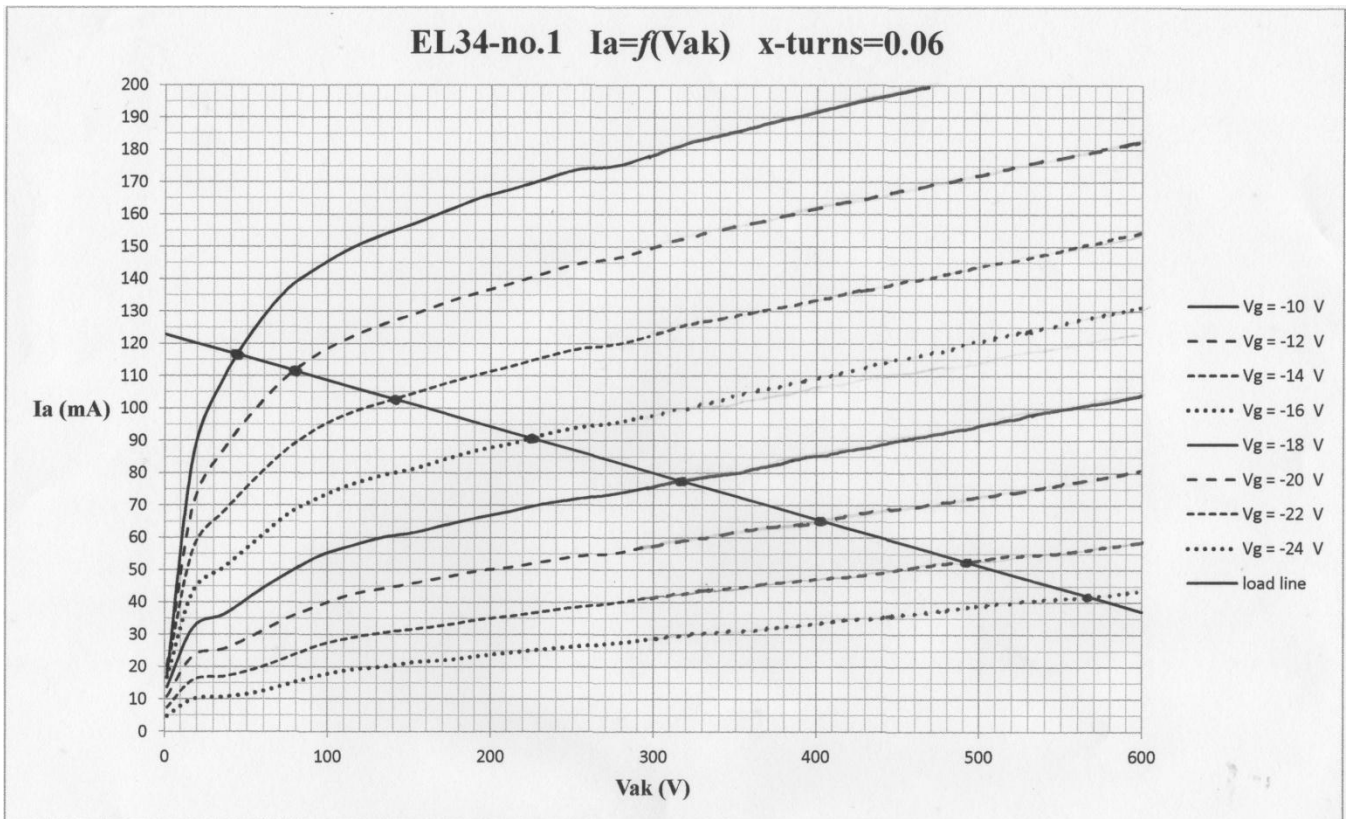
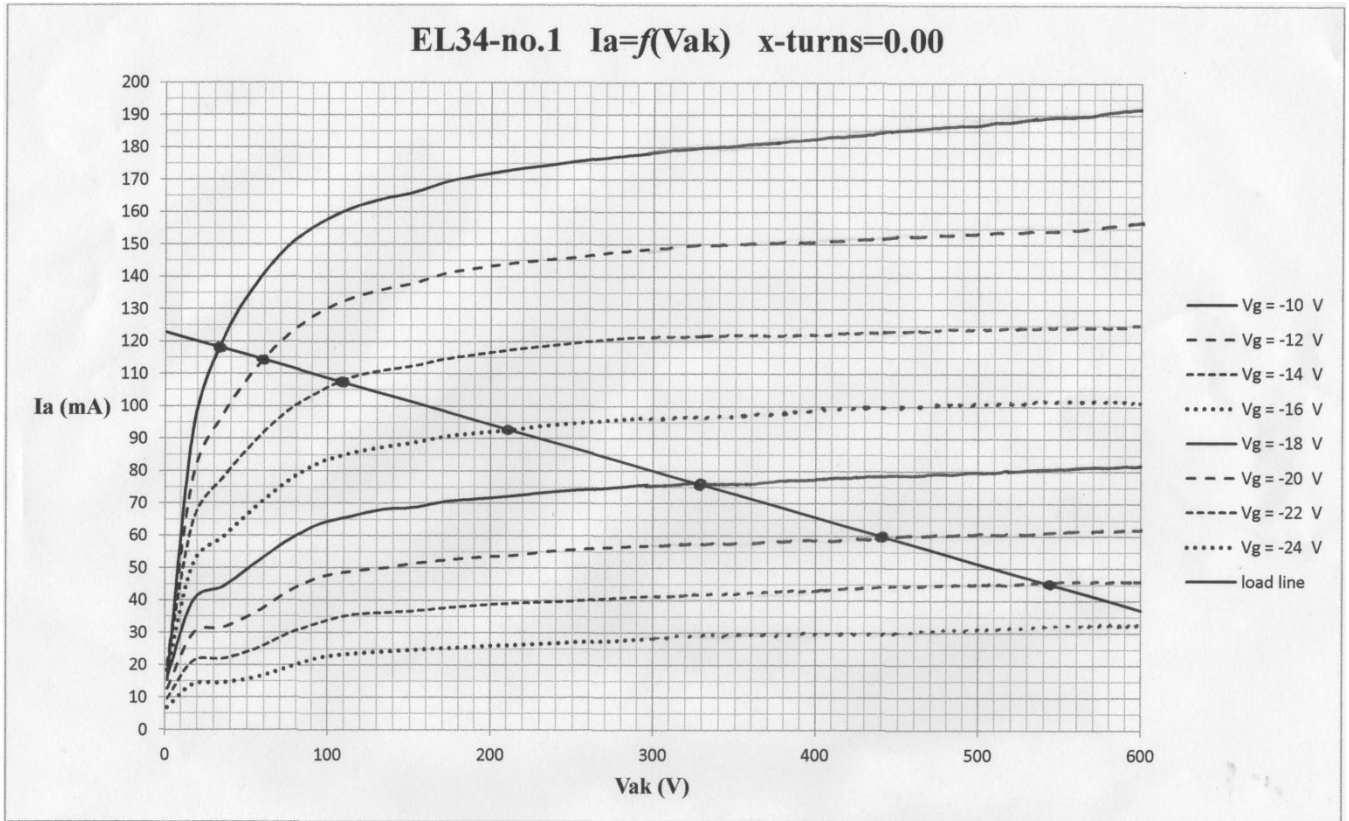
And finally all these  $S_d$  together in one transconductance characteristic.

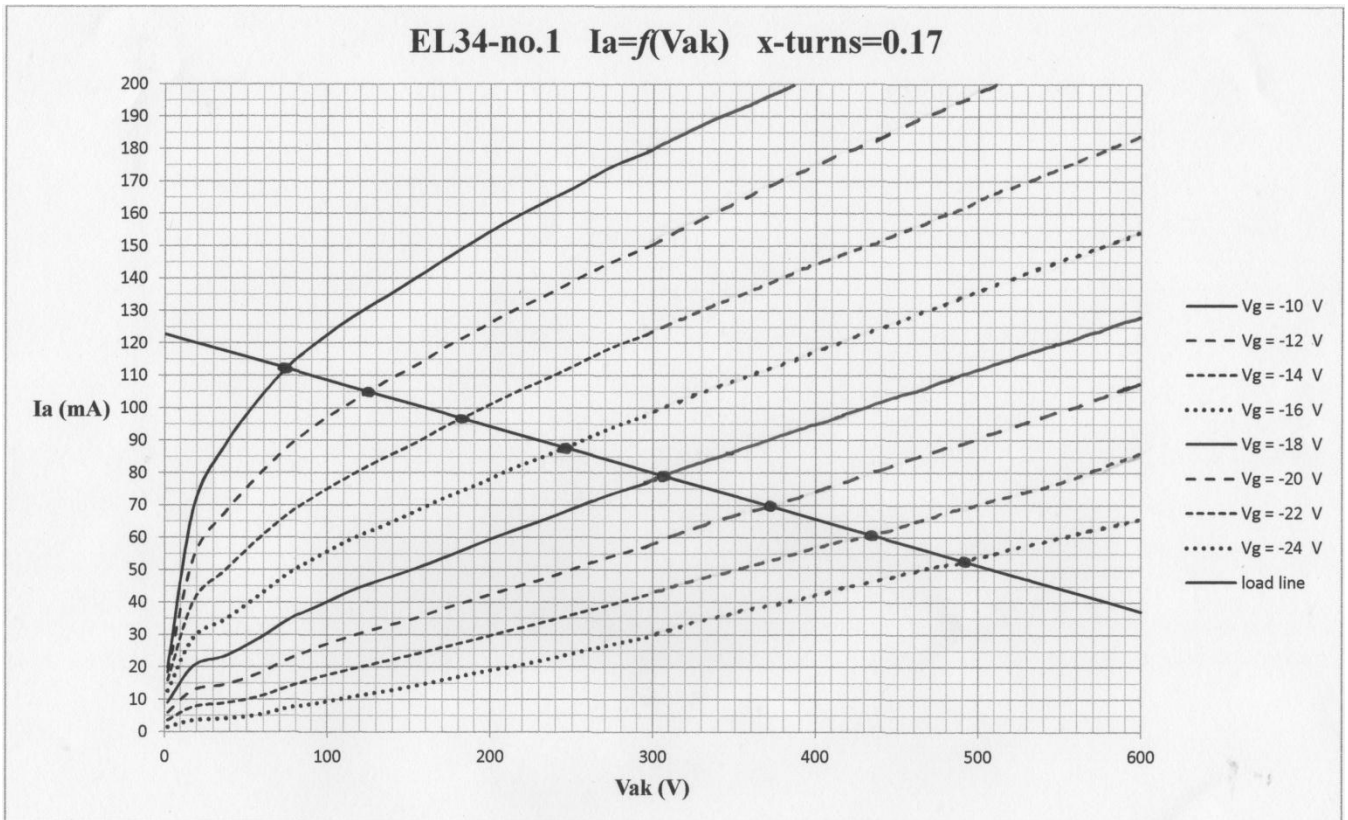
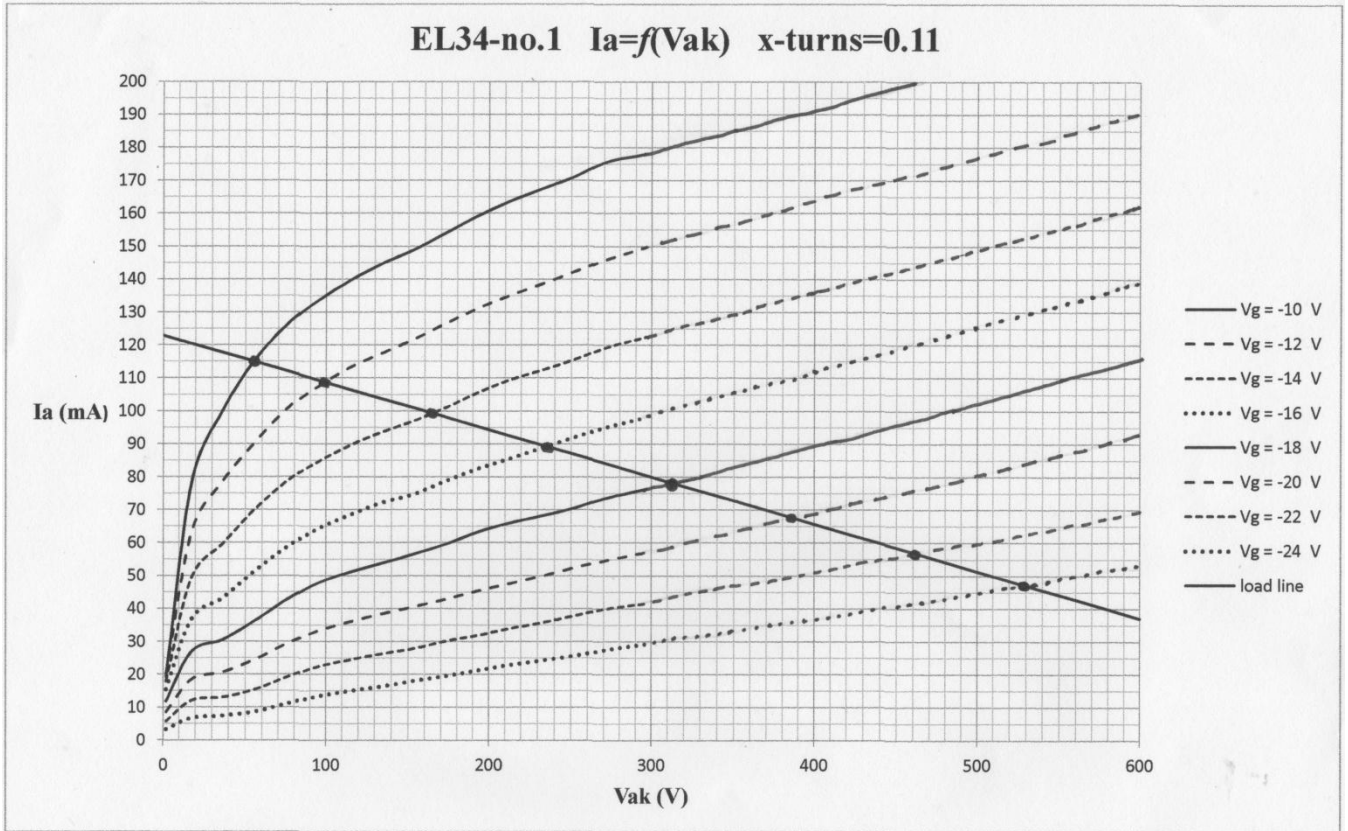


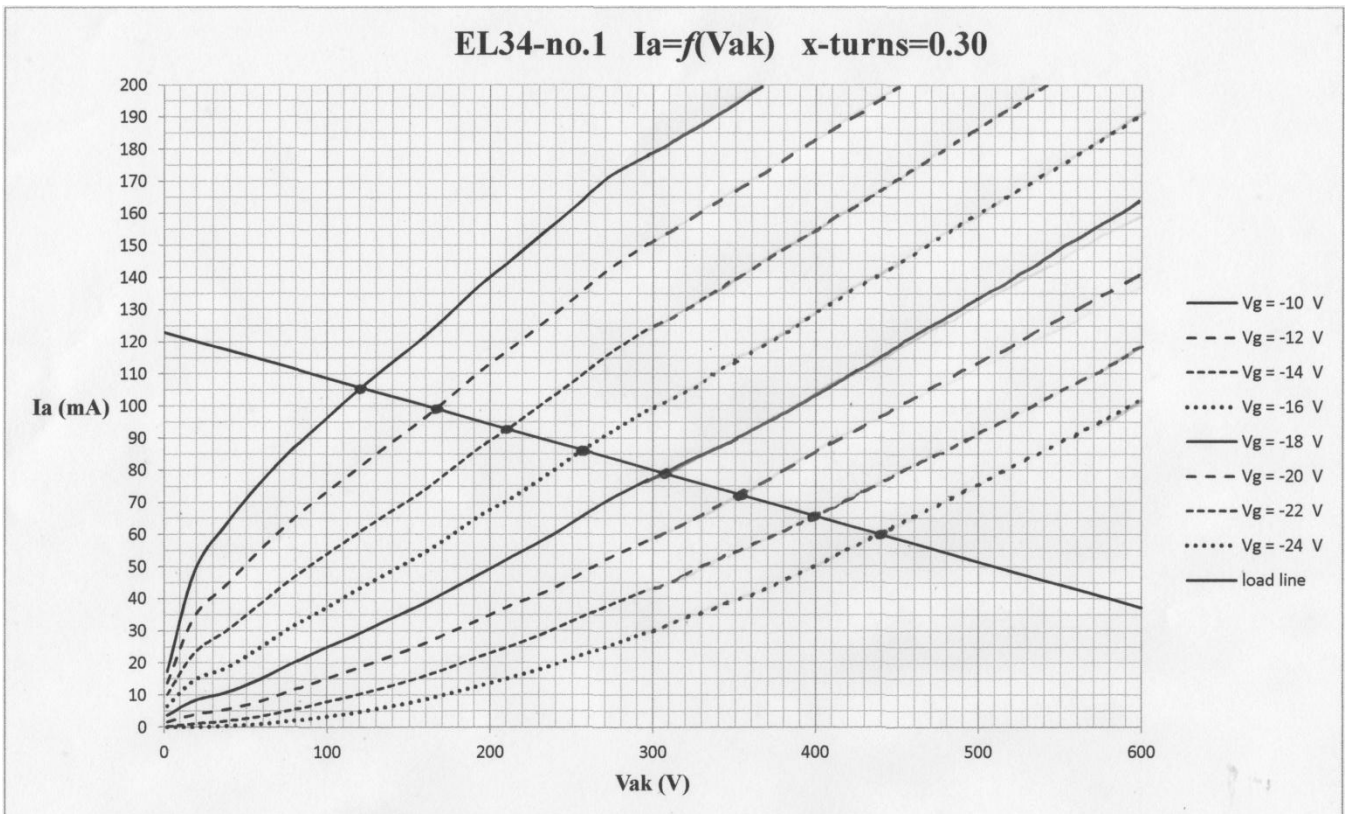
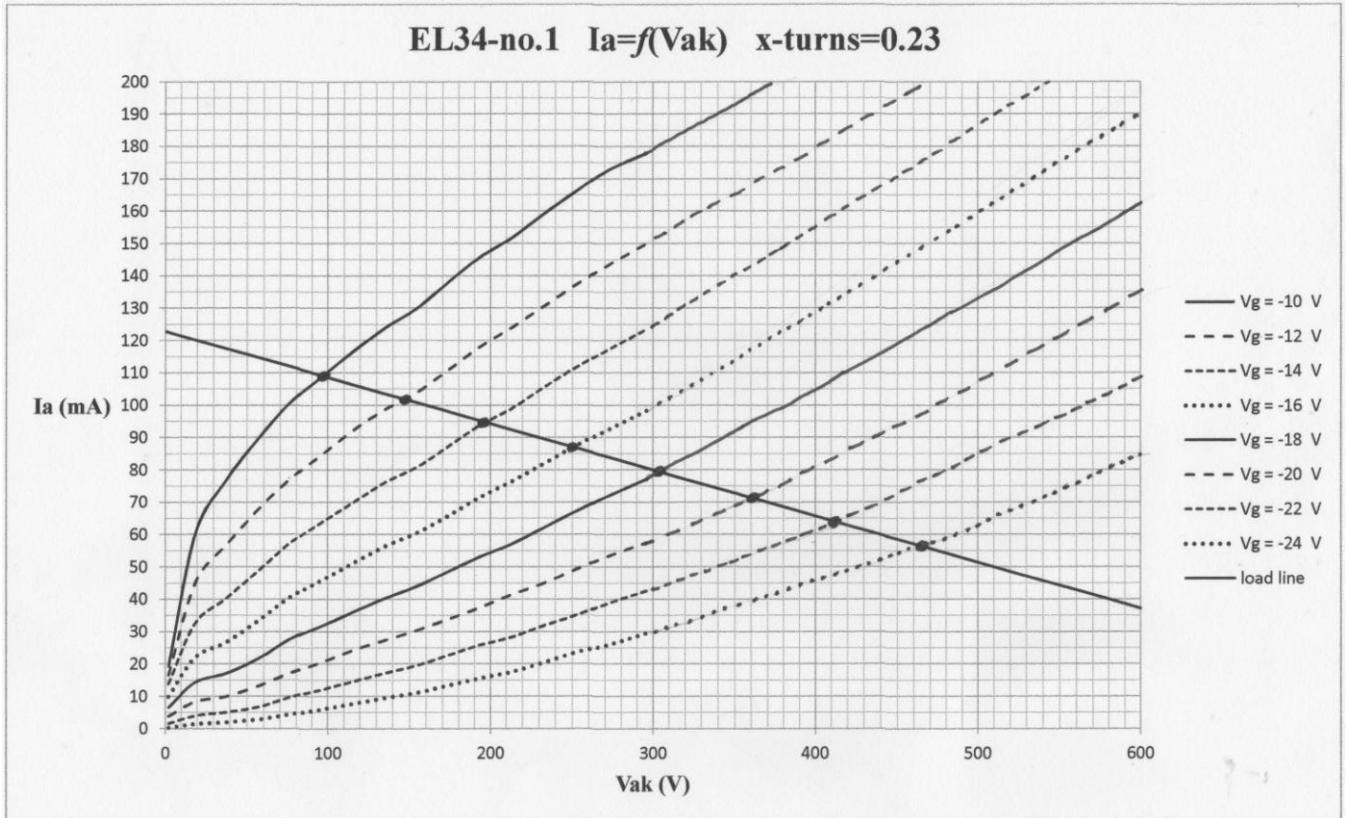


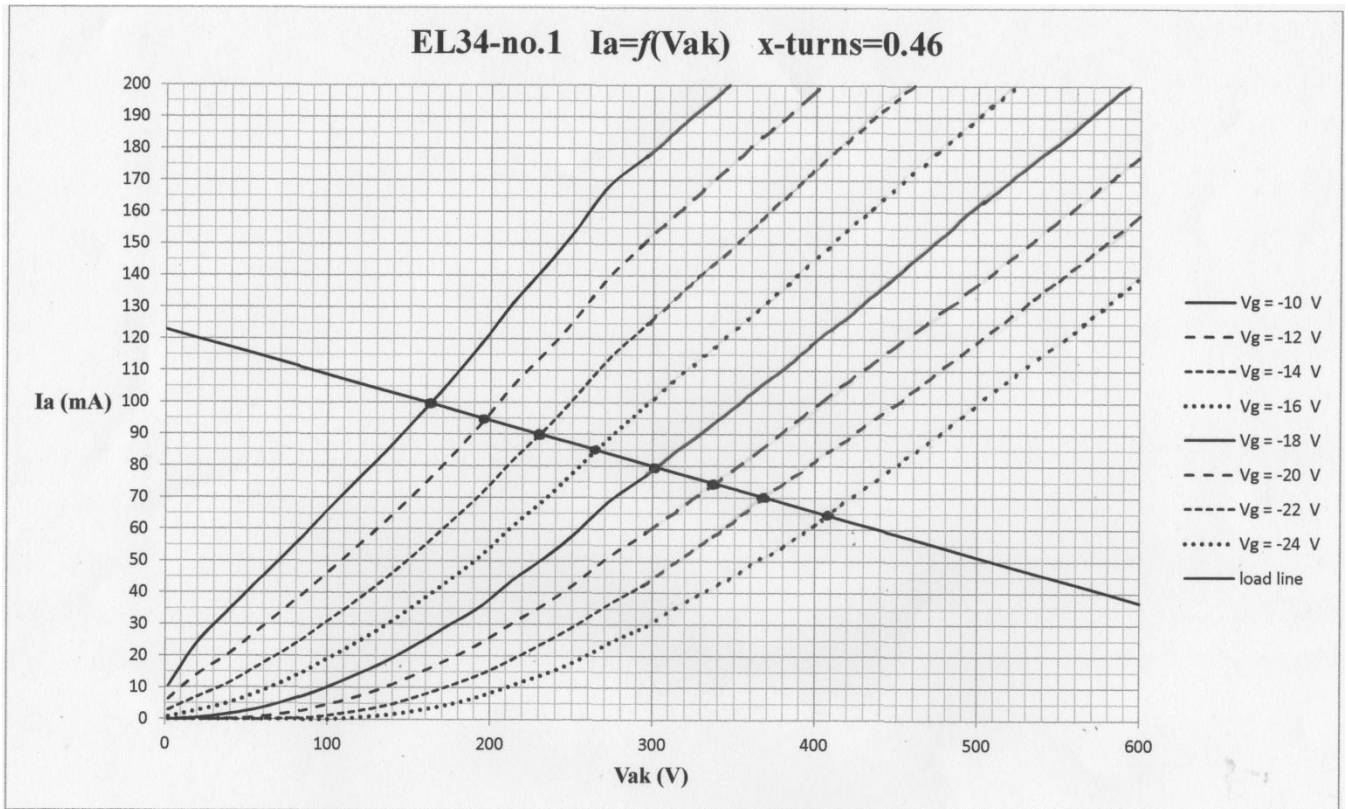
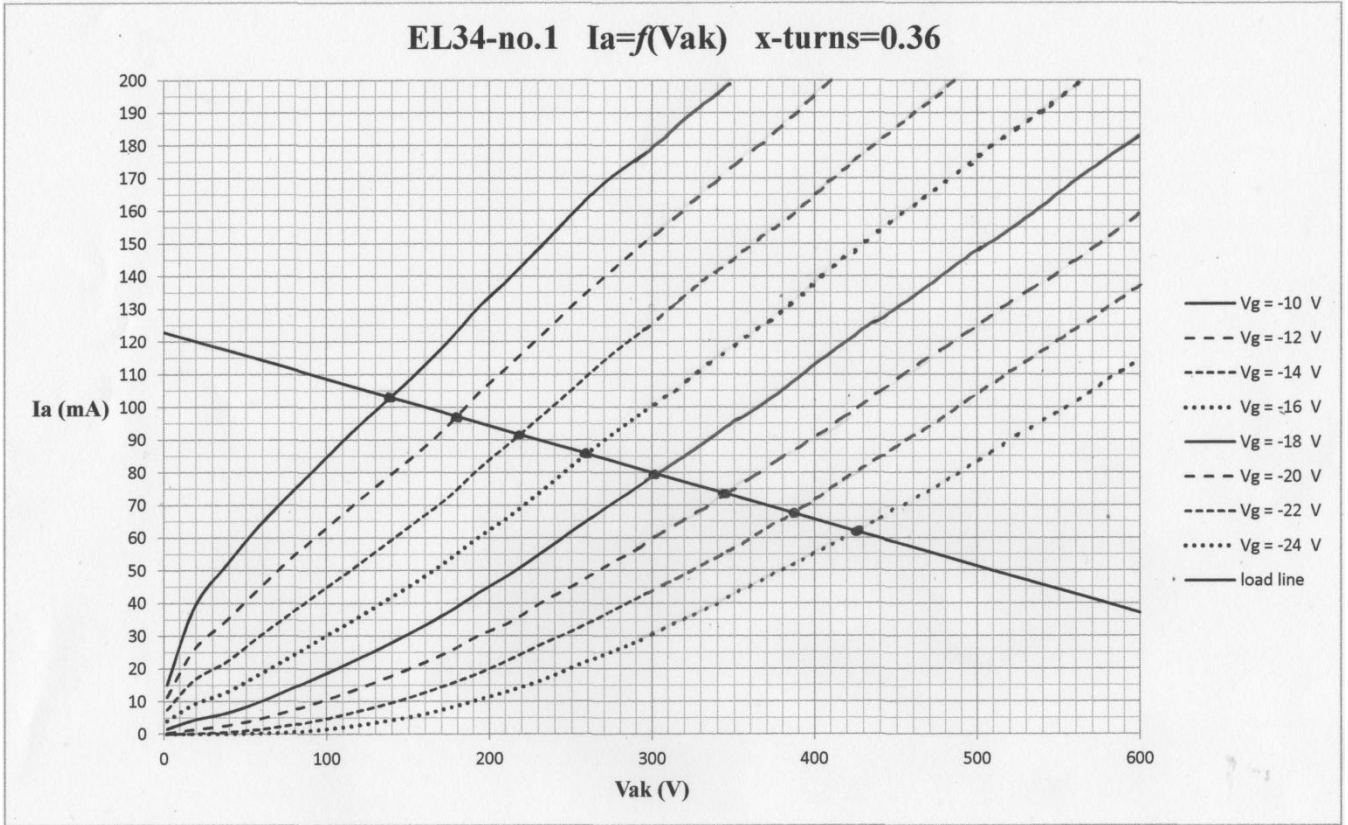
## APPENDIX C

Measured with the  $\mu$ Tracer and extrapolated anode characteristics of EL34 for several screen grid taps. Load line for EL34 goes through working point  $V_{ak,w} = 300\text{V}$ ,  $I_{a,w} = 80\text{mA}$  and  $V_{gIk,w} \approx -16.1\text{V}$ .

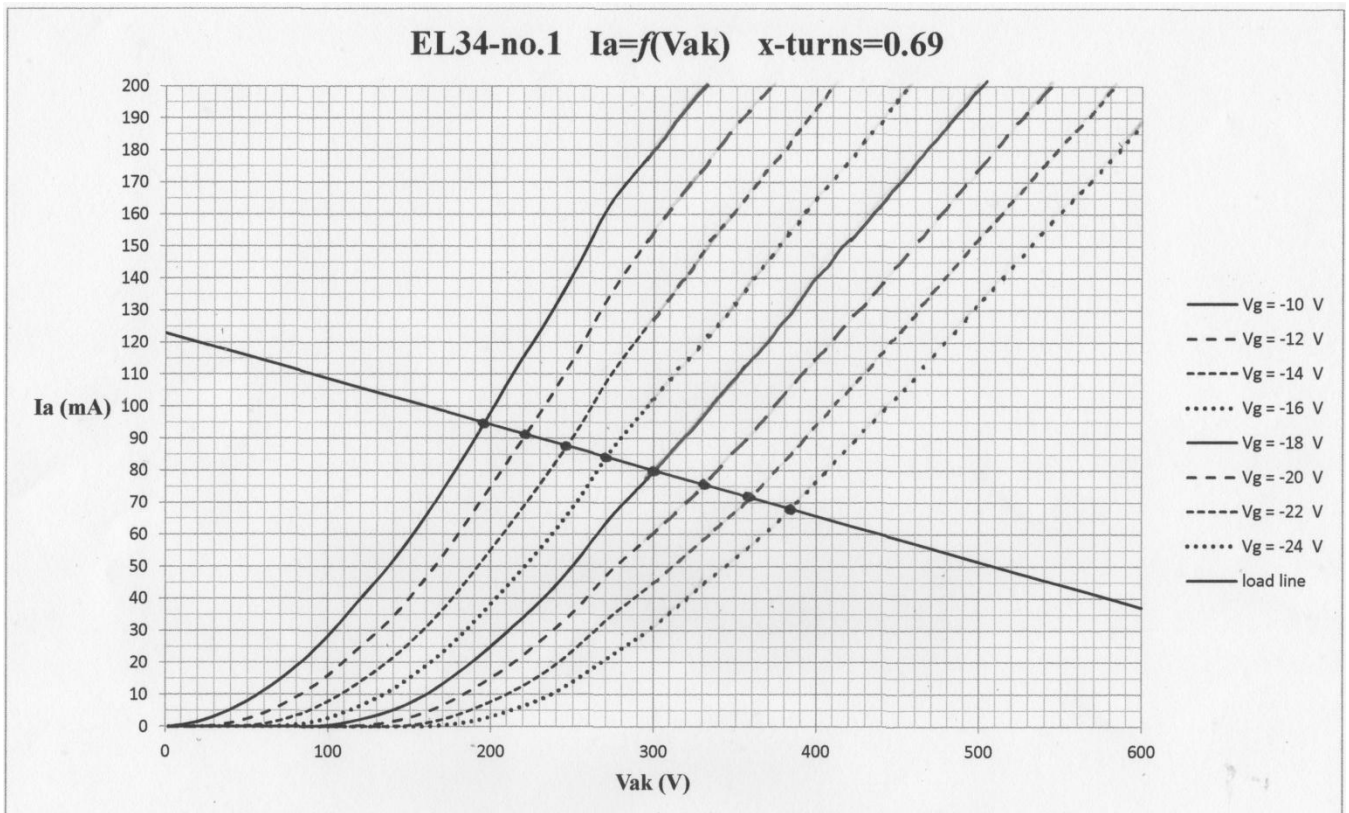
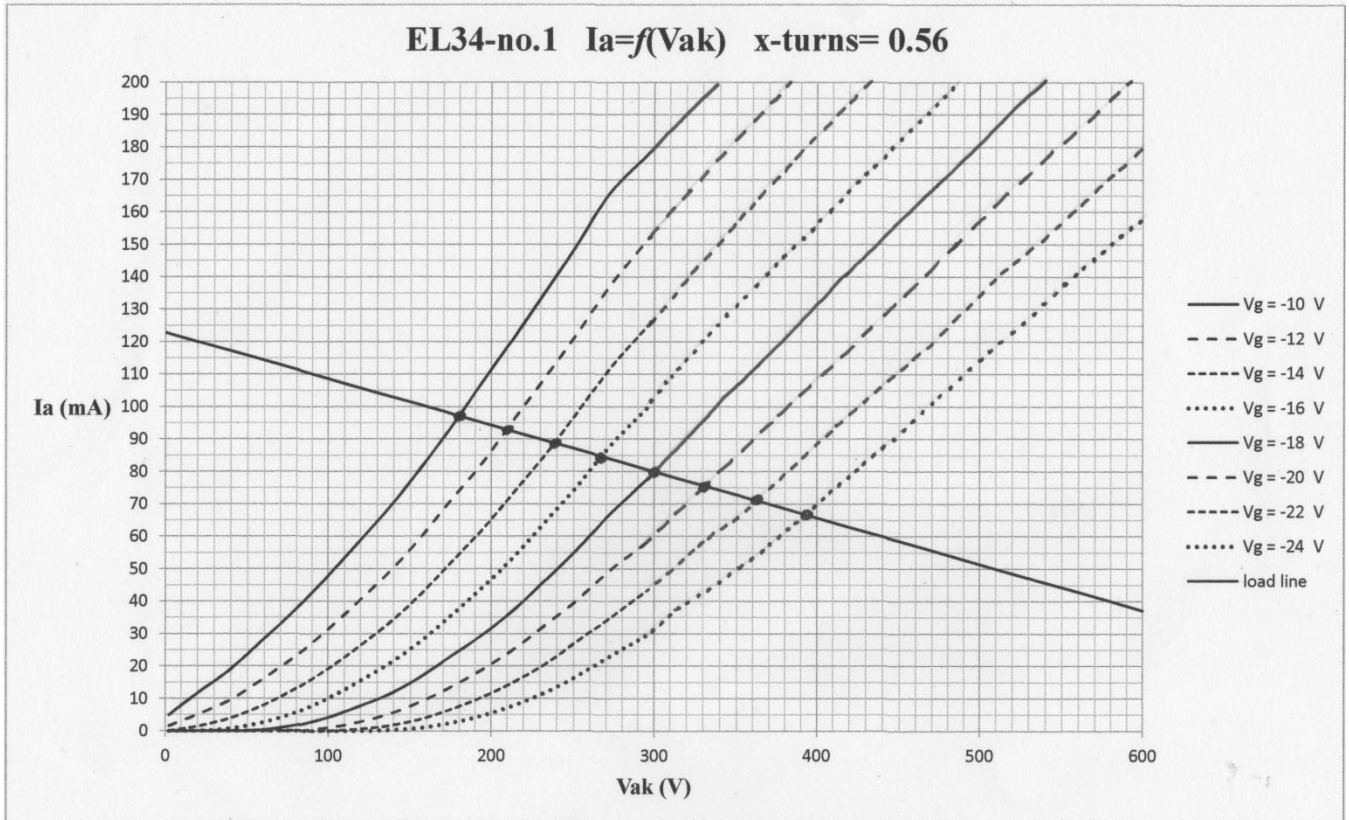










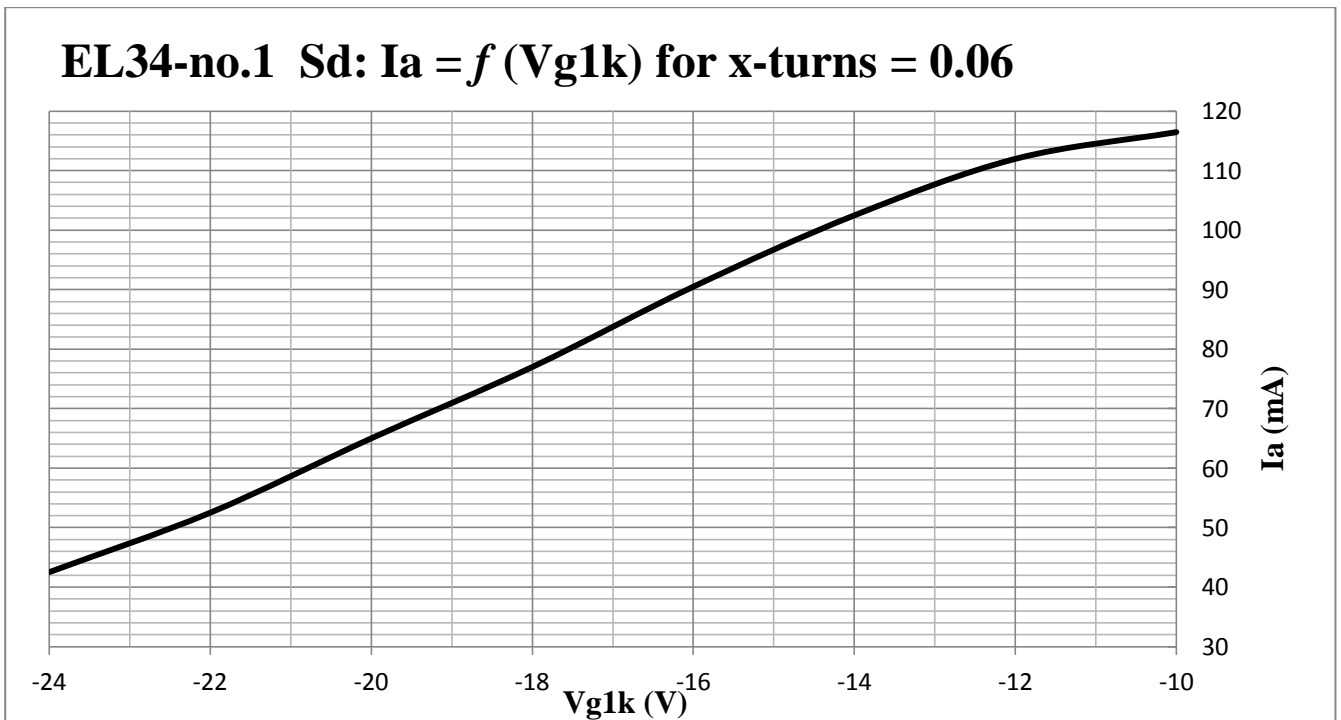
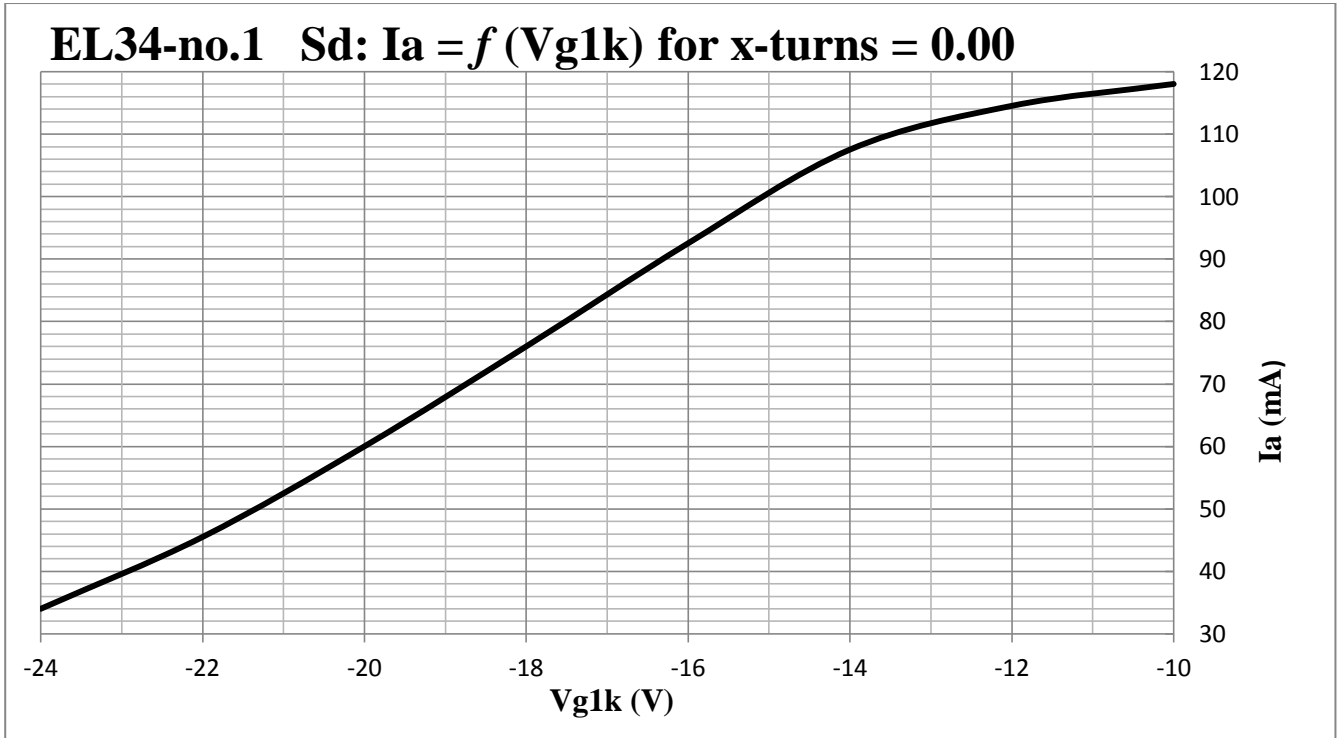


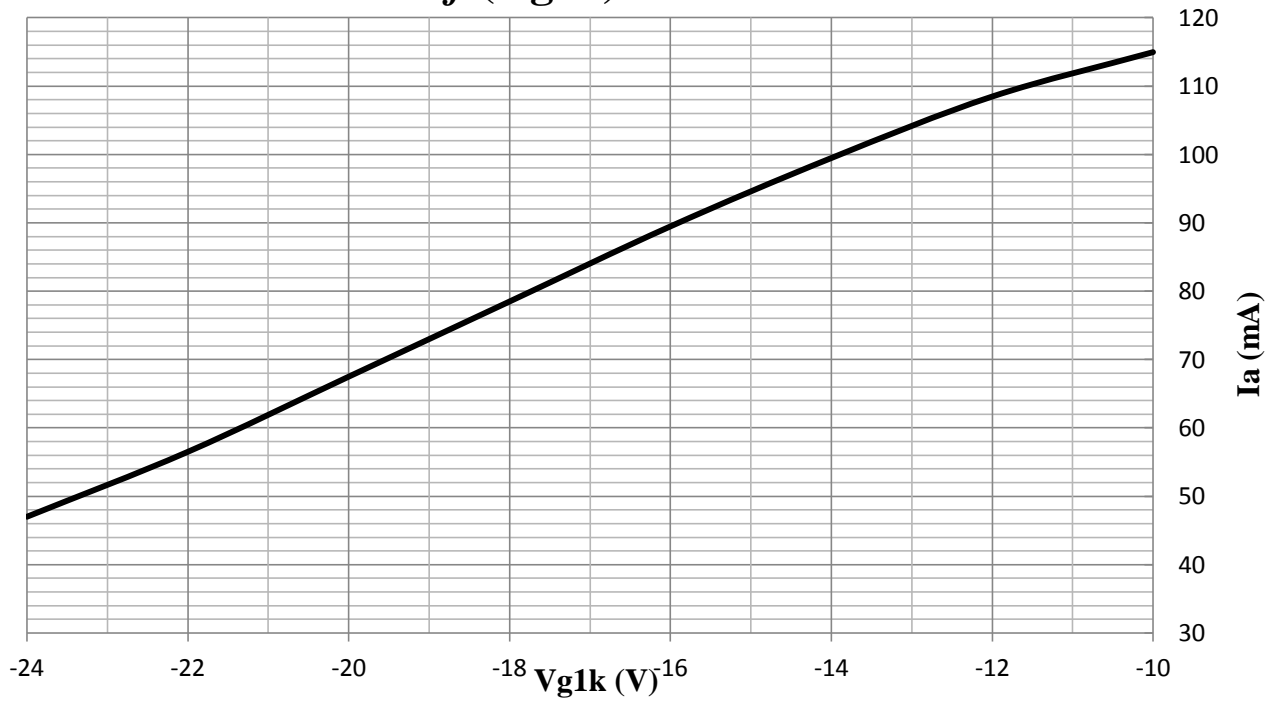
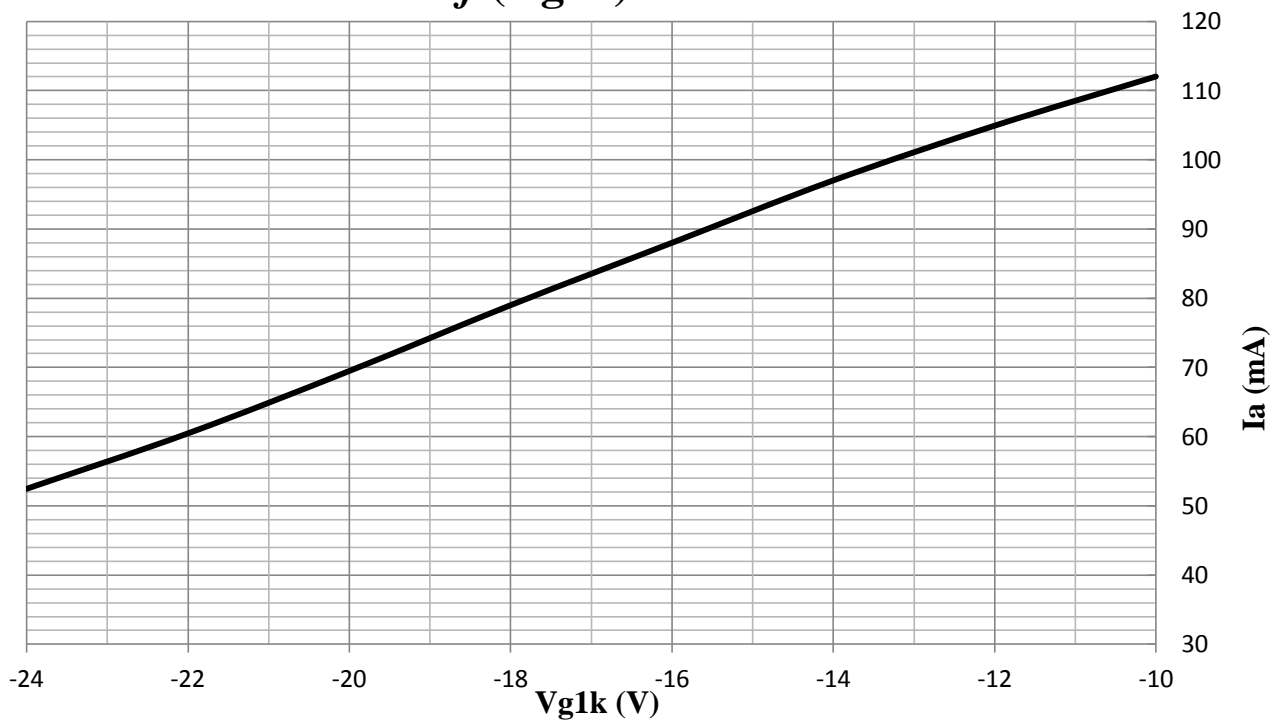


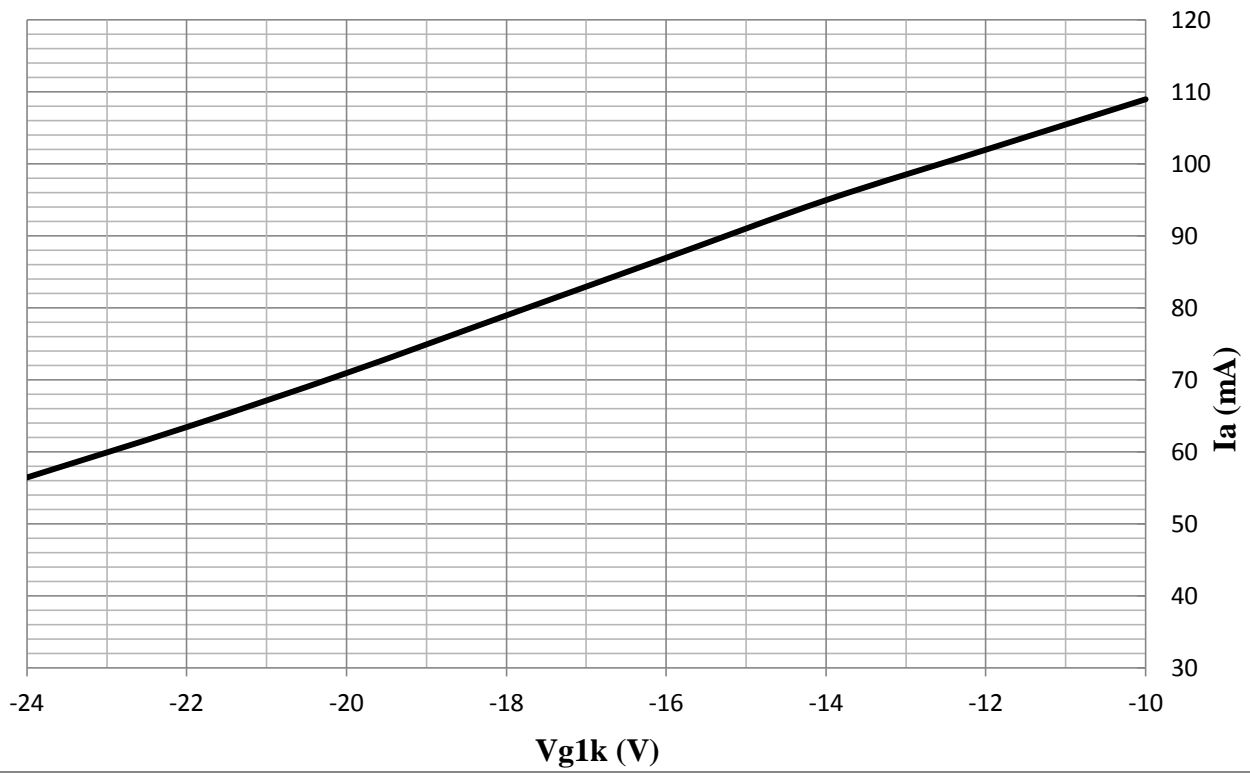
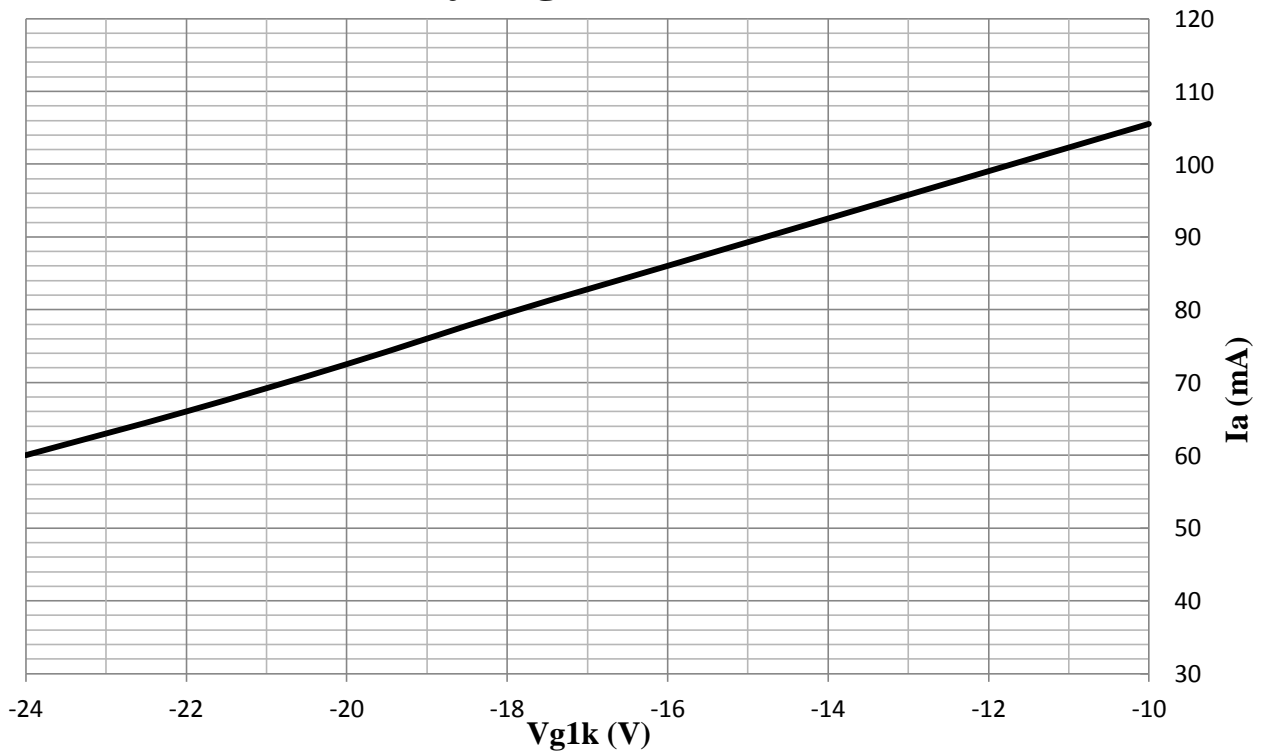


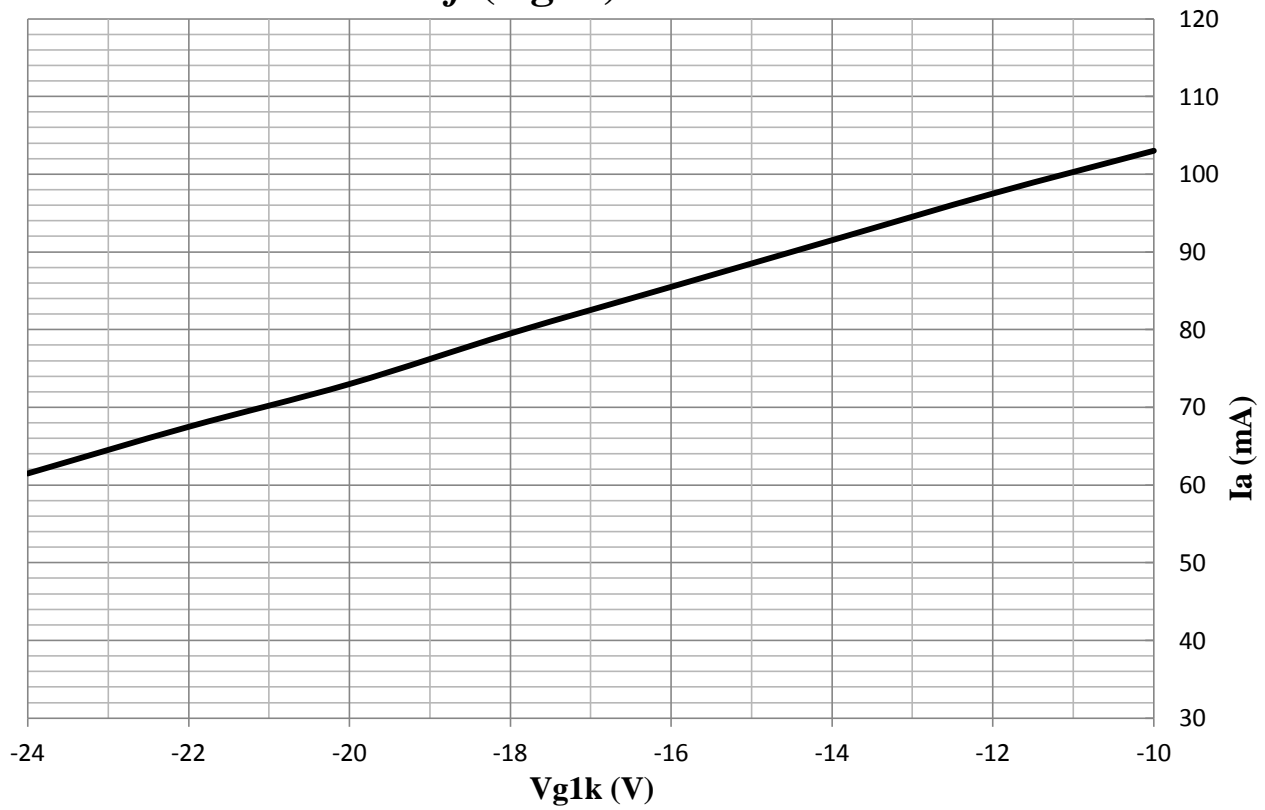
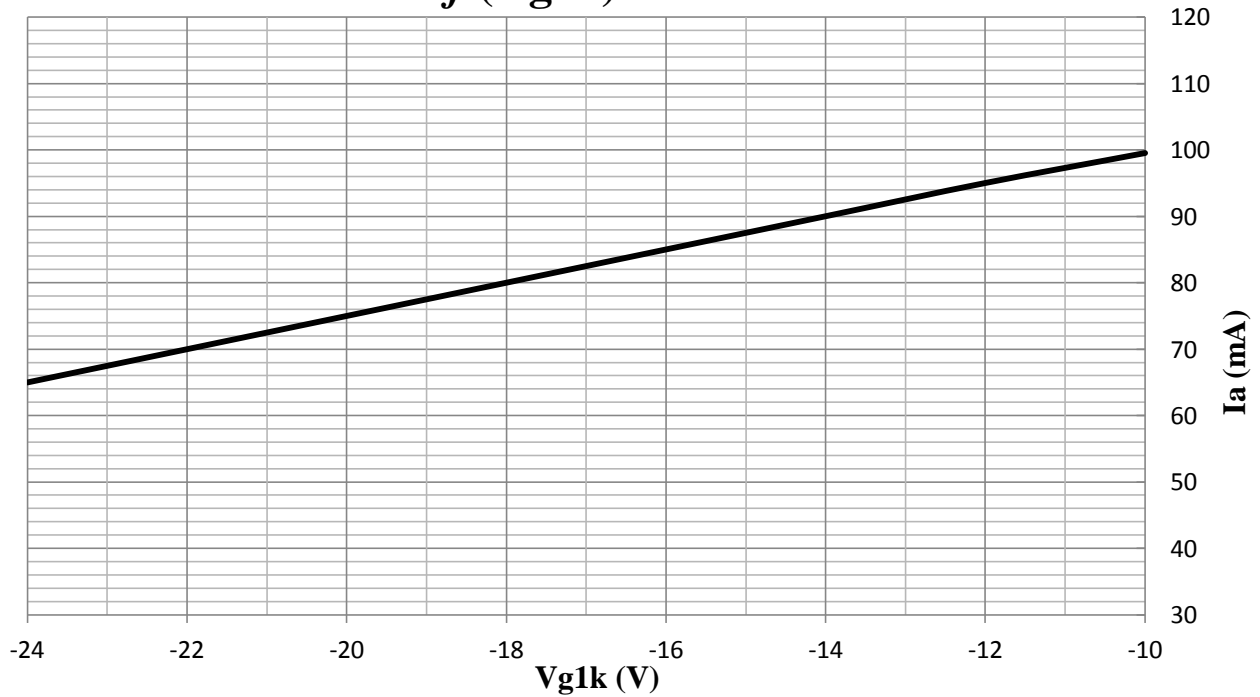
## APPENDIX D

Constructed dynamic transconductance characteristics of EL34 for several screen grid taps.

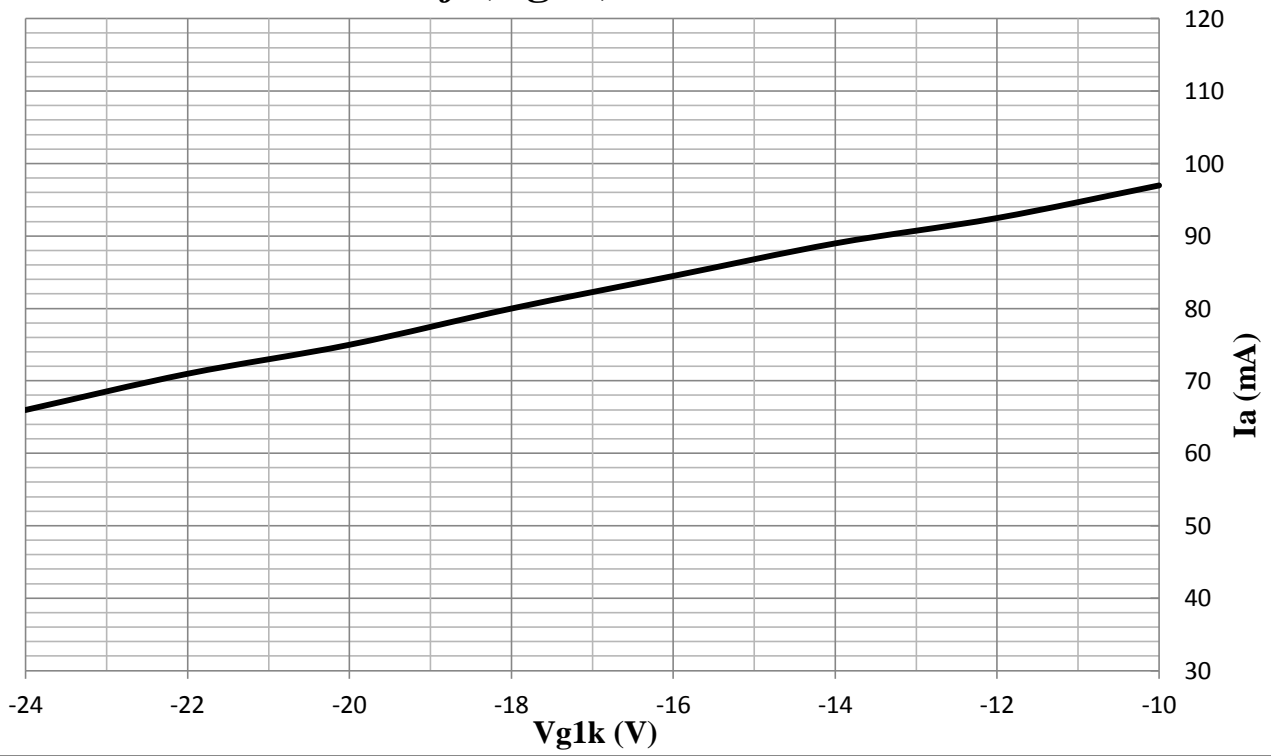
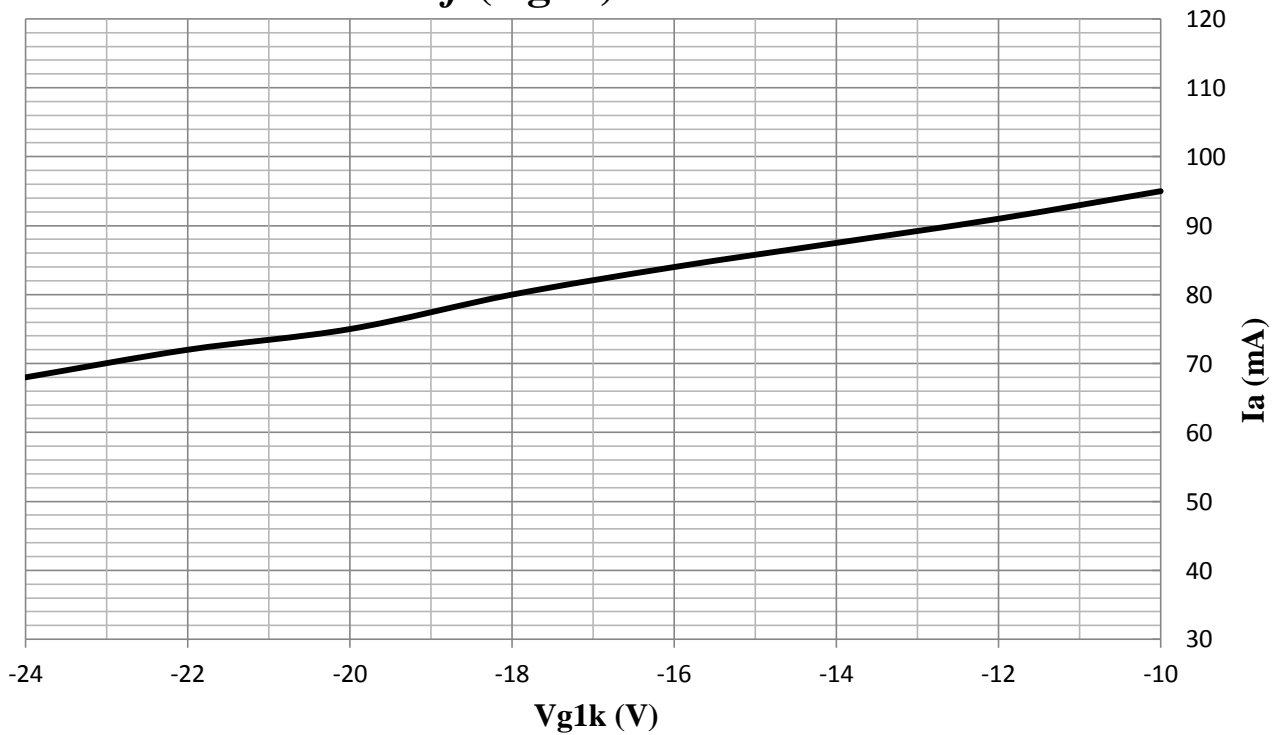


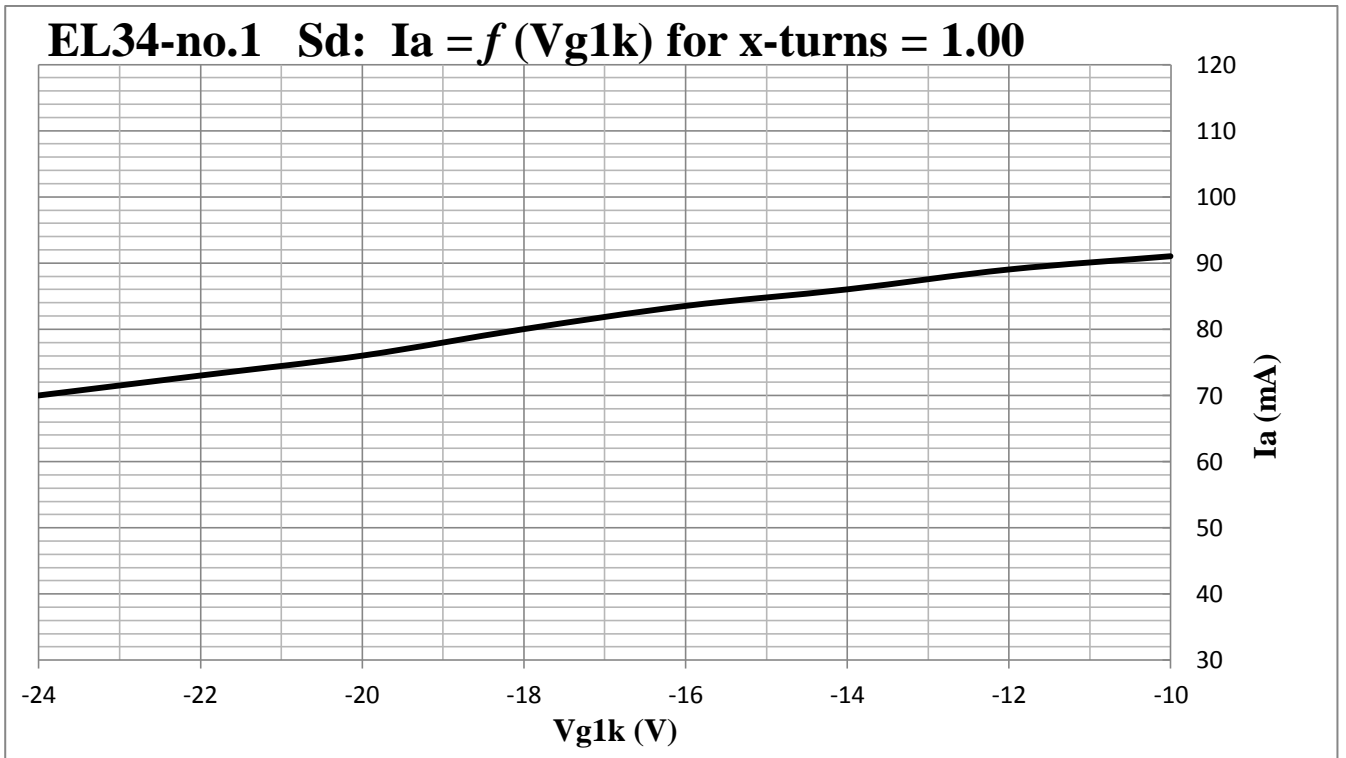
**EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.11****EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.17**

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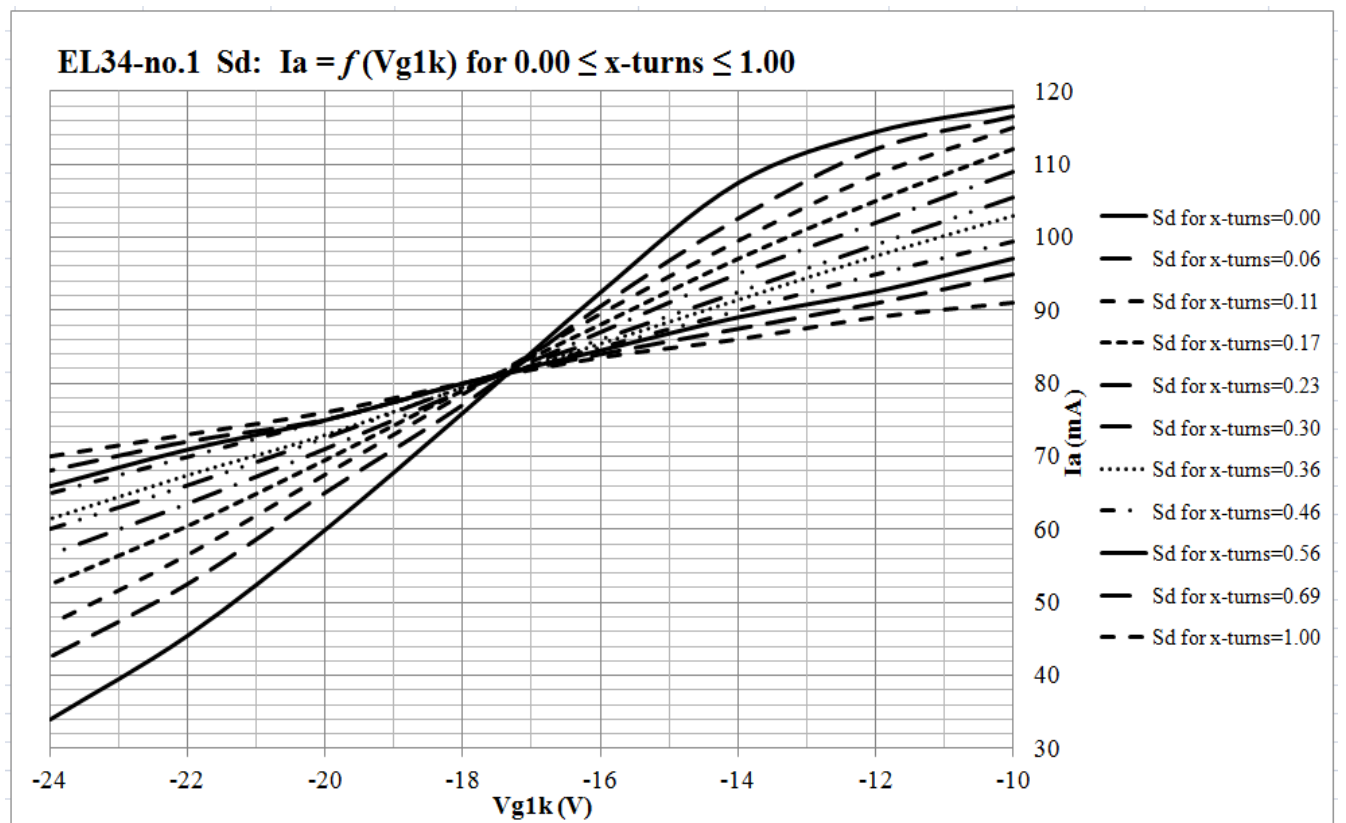
**EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.36****EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.46**



**EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.56****EL34-no.1 Sd:  $I_a = f(V_{g1k})$  for x-turns = 0.69**

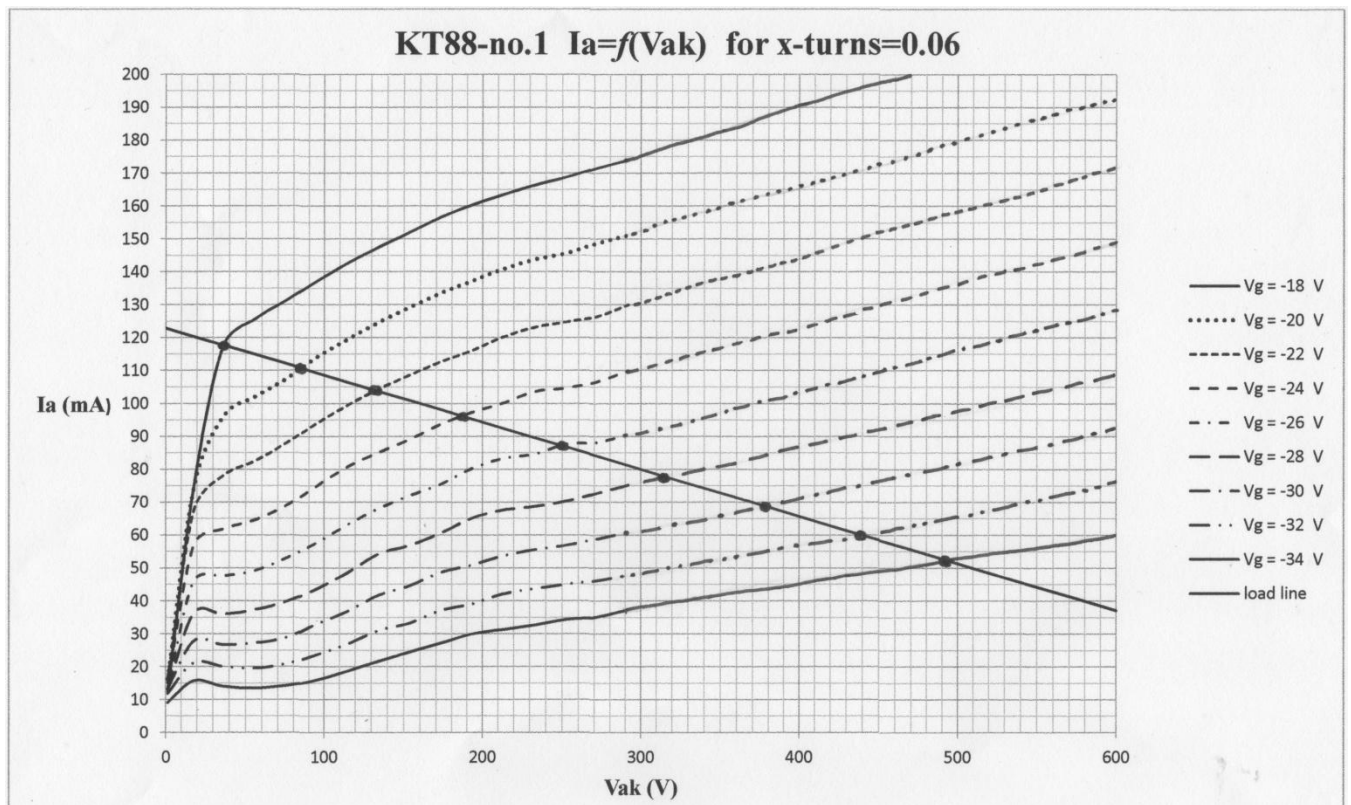
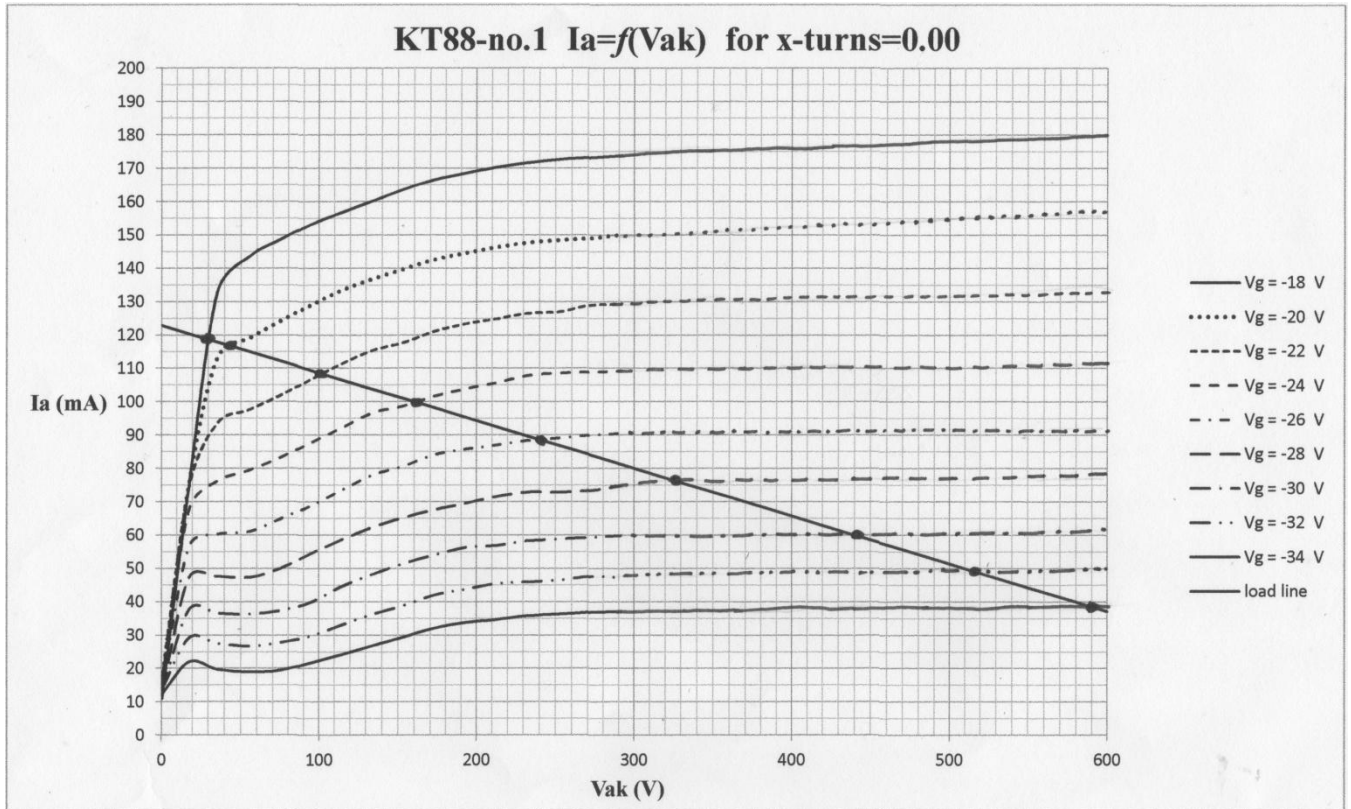


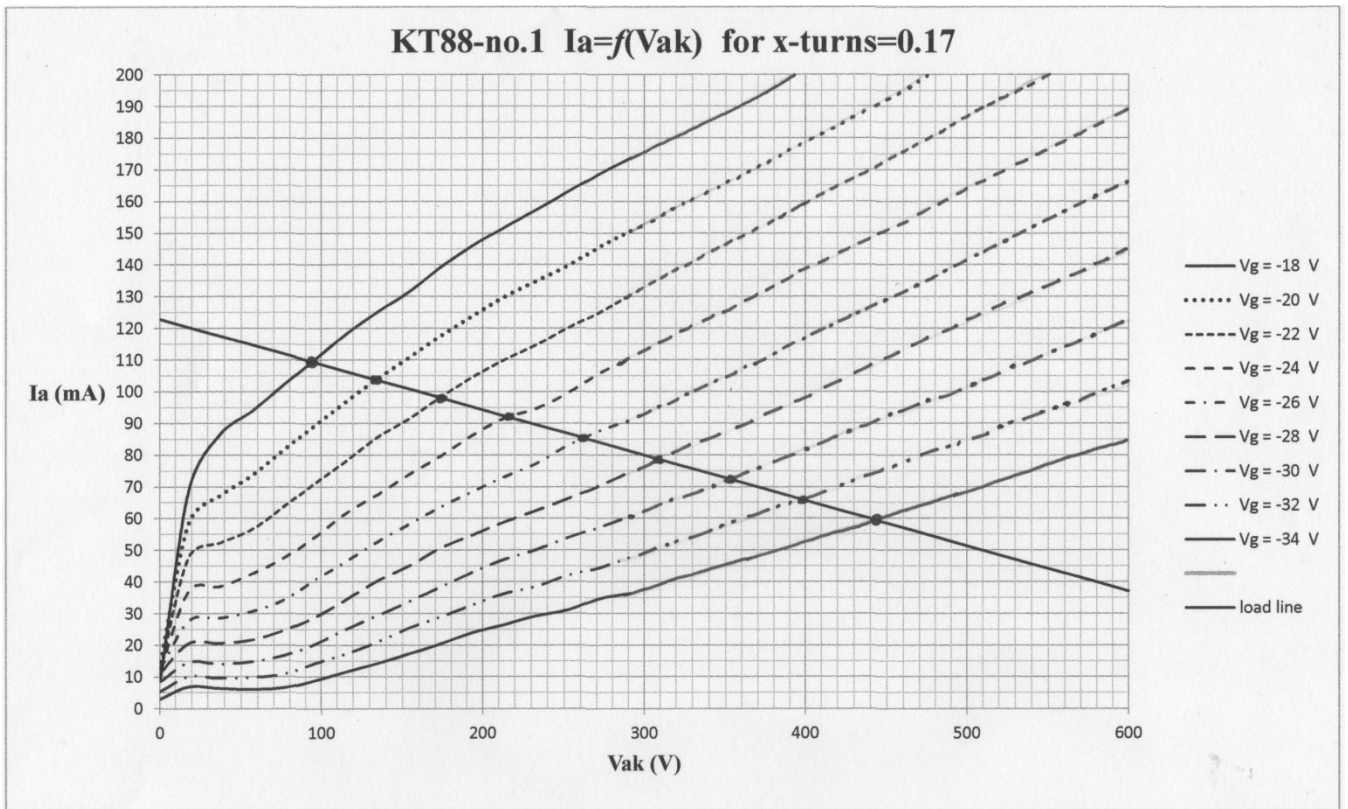
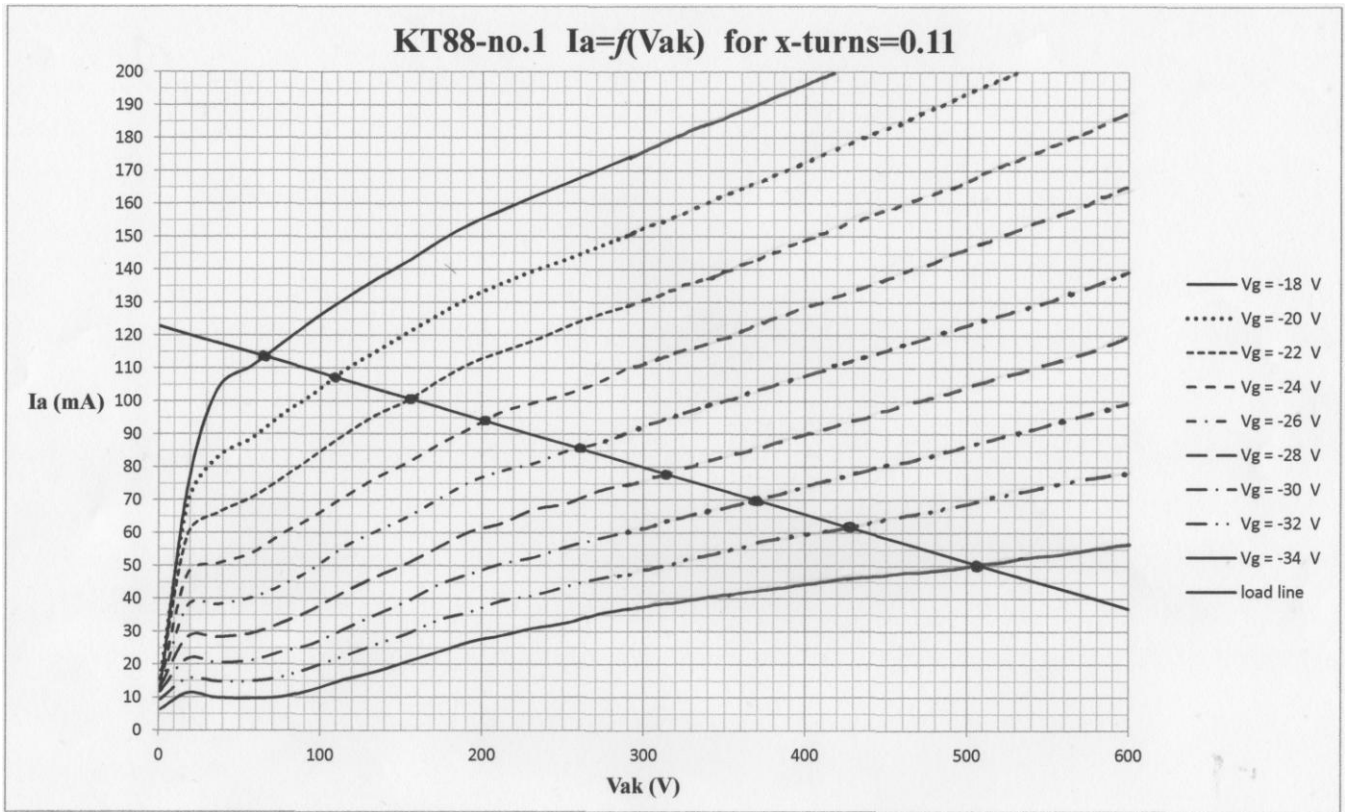
And finally all these  $S_d$  together in one transconductance characteristic.

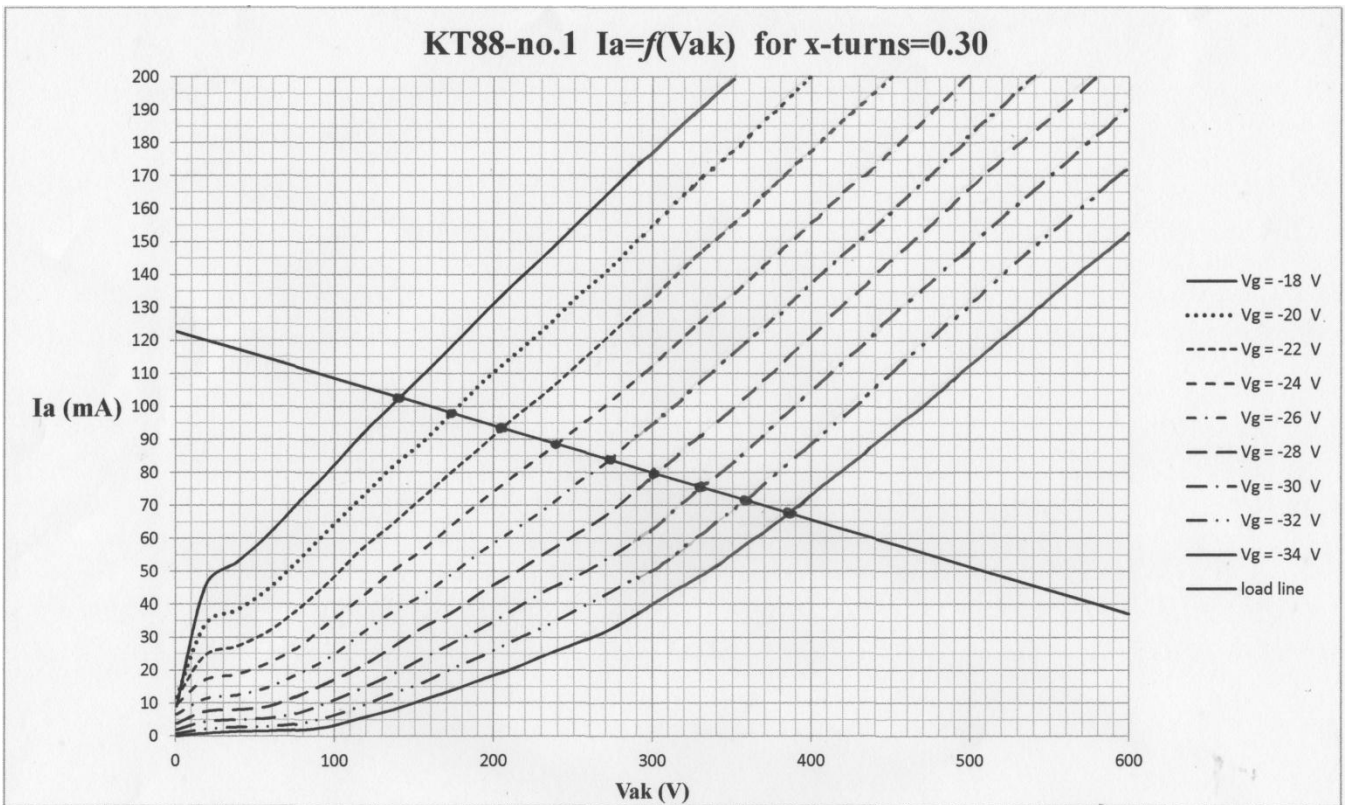
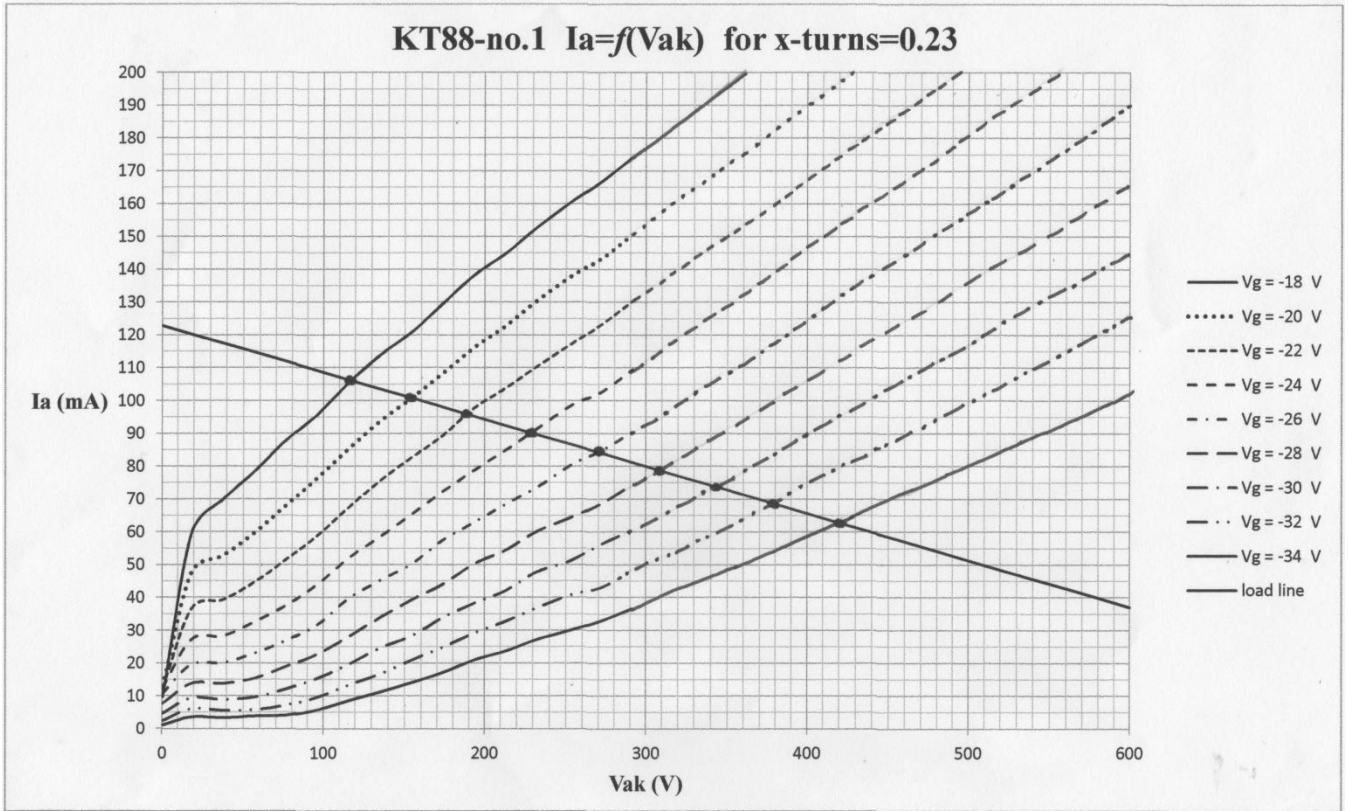


## APPENDIX E

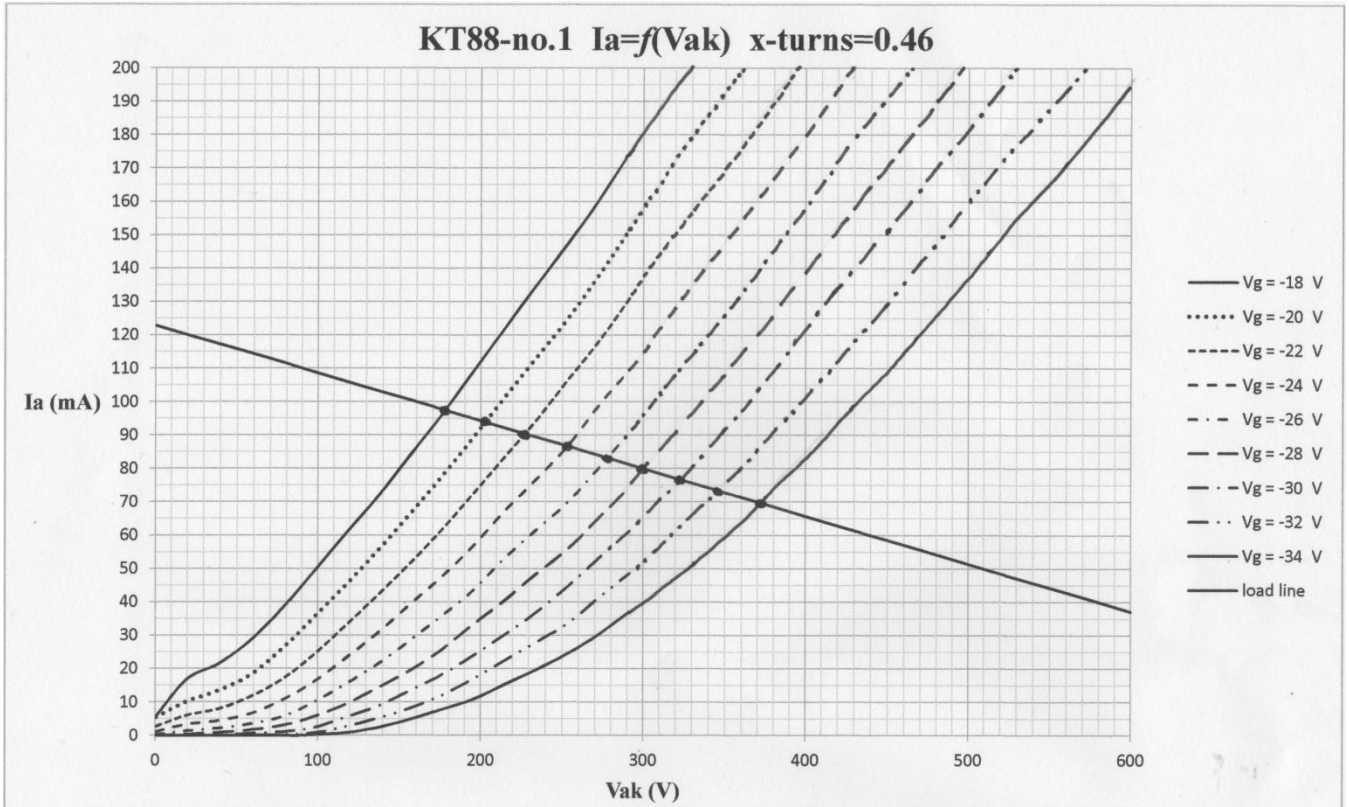
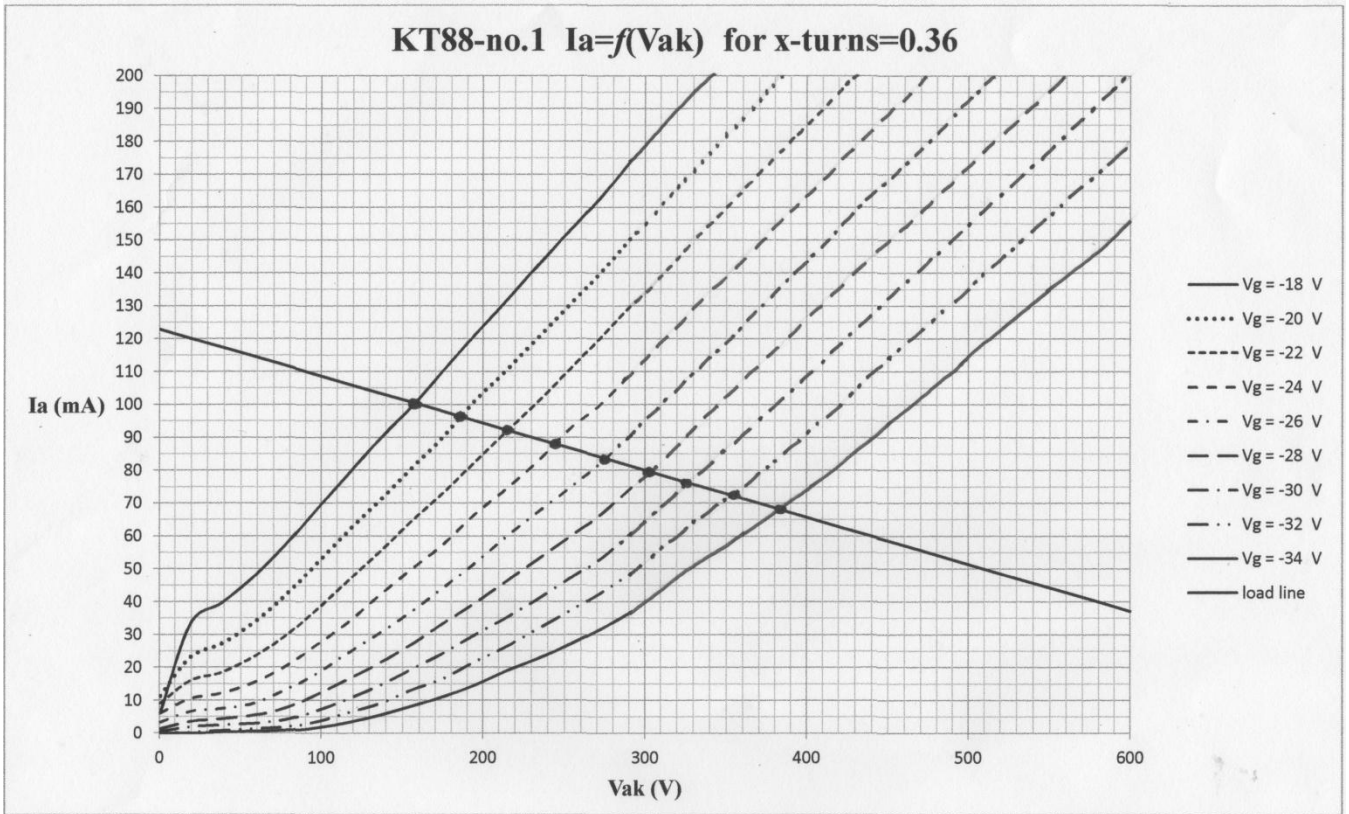
Measured with the  $\mu$ Tracer and extrapolated anode characteristics of KT88 for several screen grid taps. Load line for KT88 goes through working point  $V_{ak,w} = 300\text{V}$ ,  $I_{a,w} = 80\text{mA}$  and  $V_{g1k,w} \approx -26.4\text{V}$ .

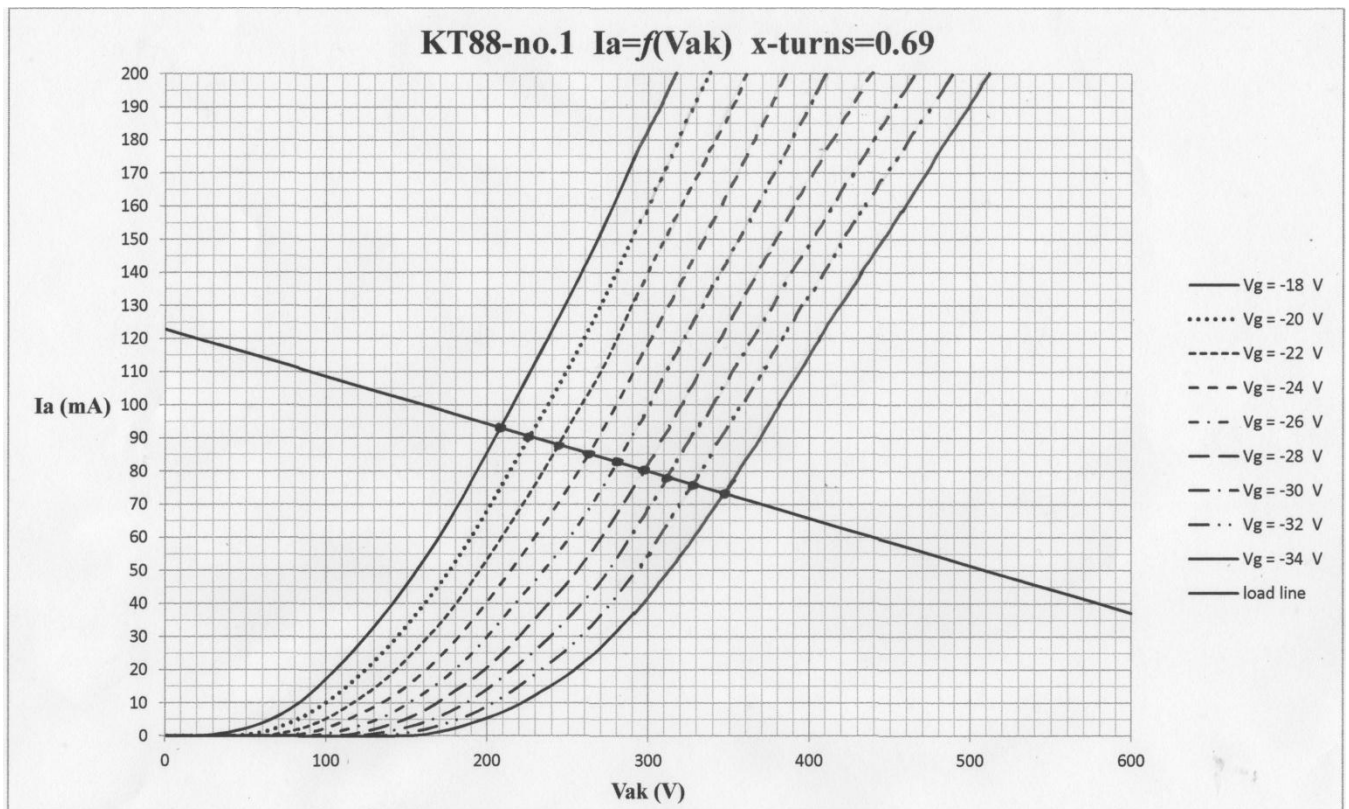
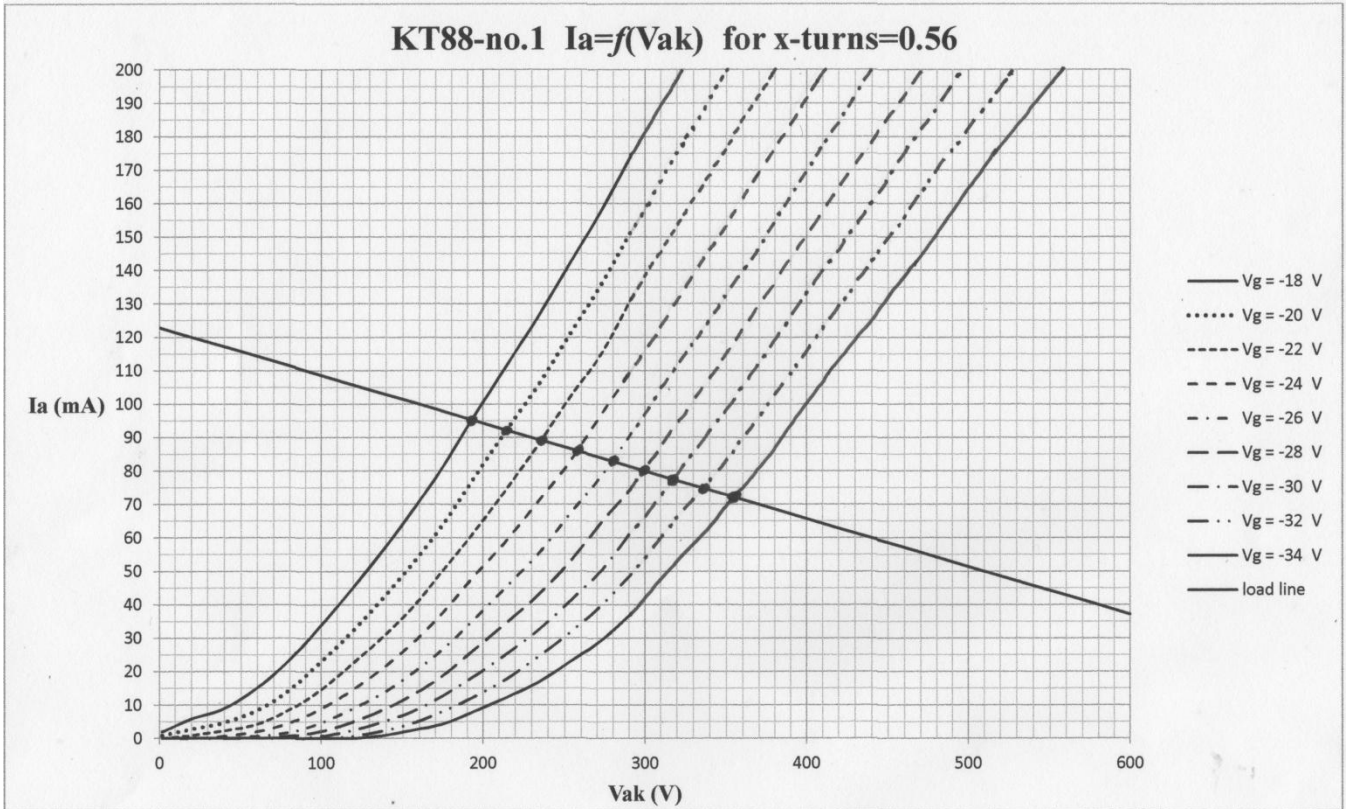








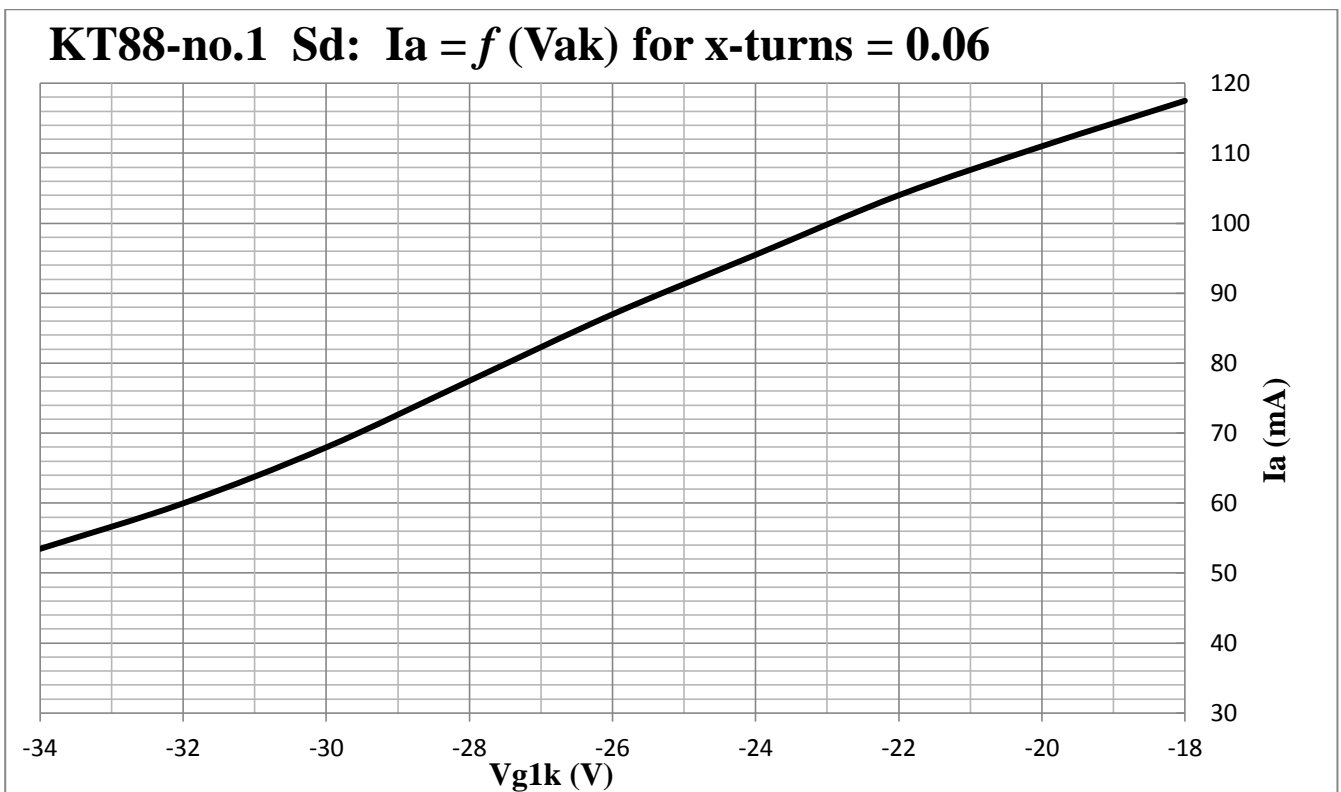
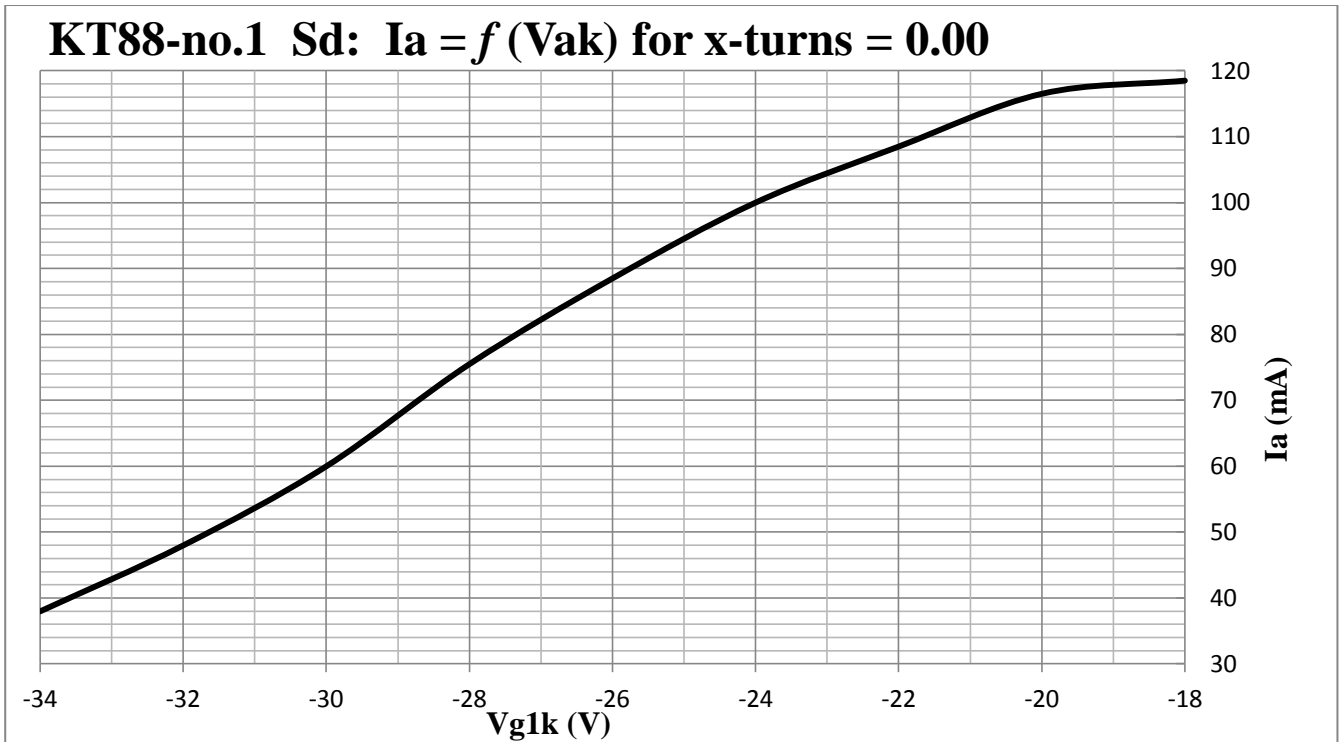


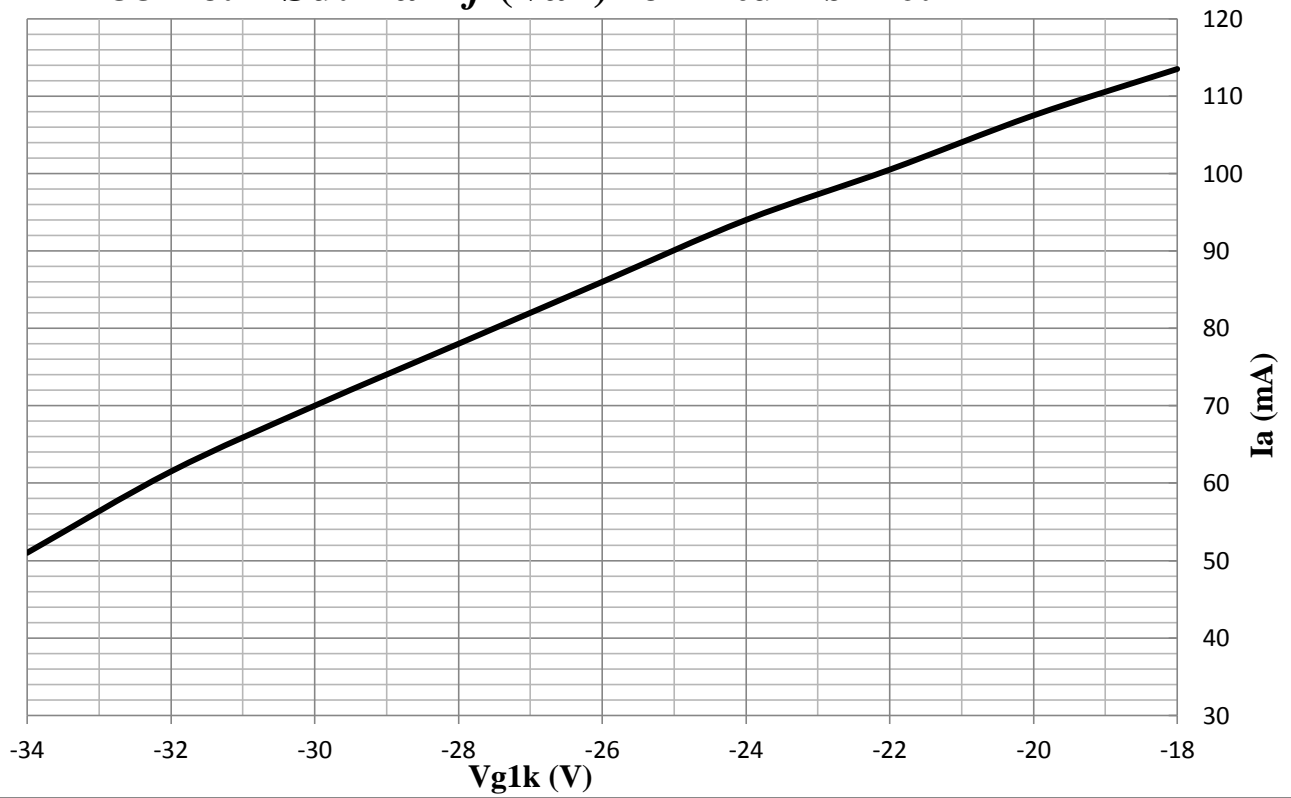
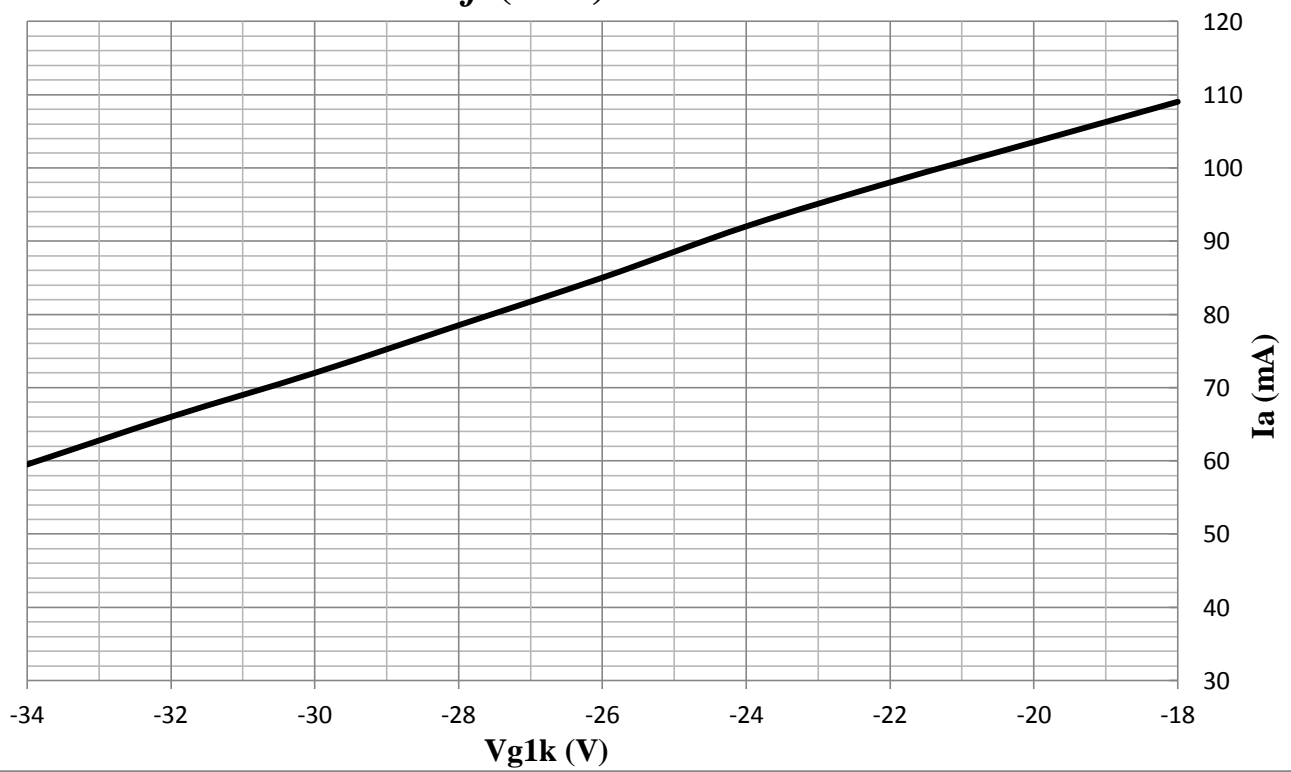


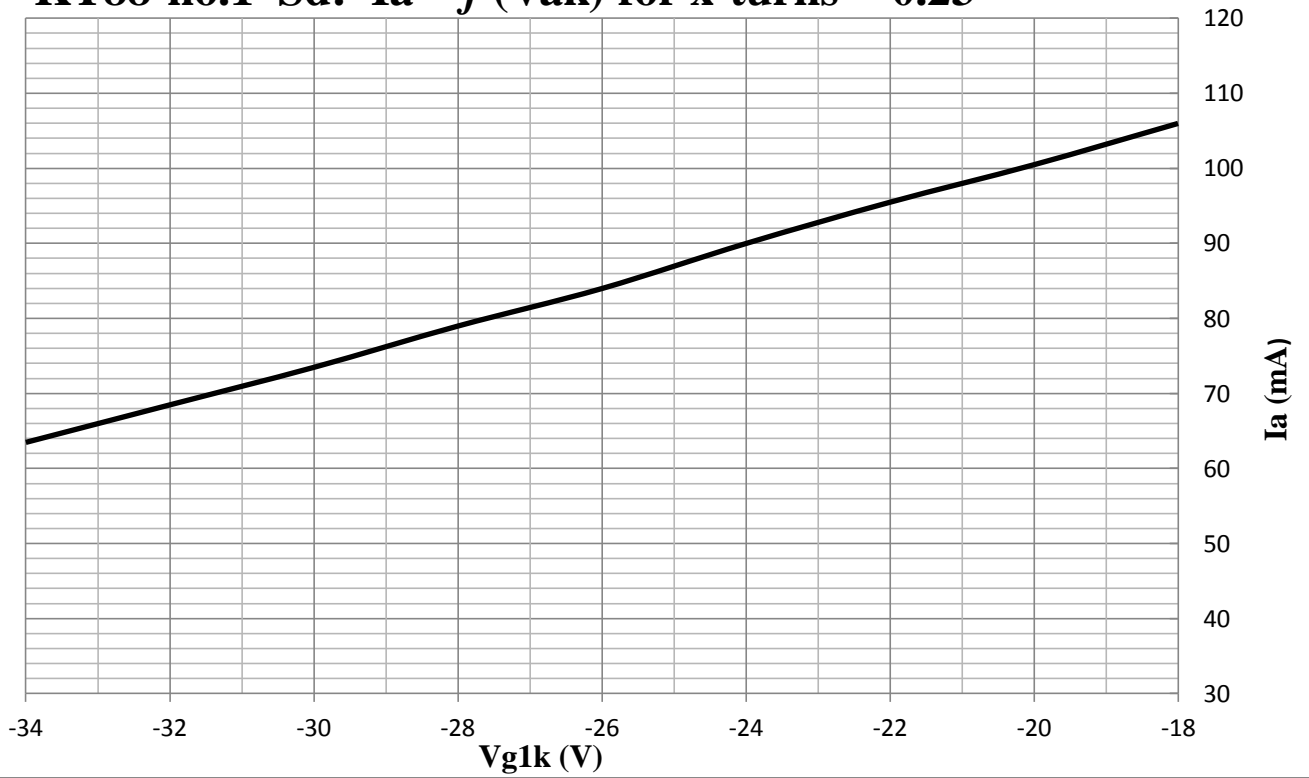
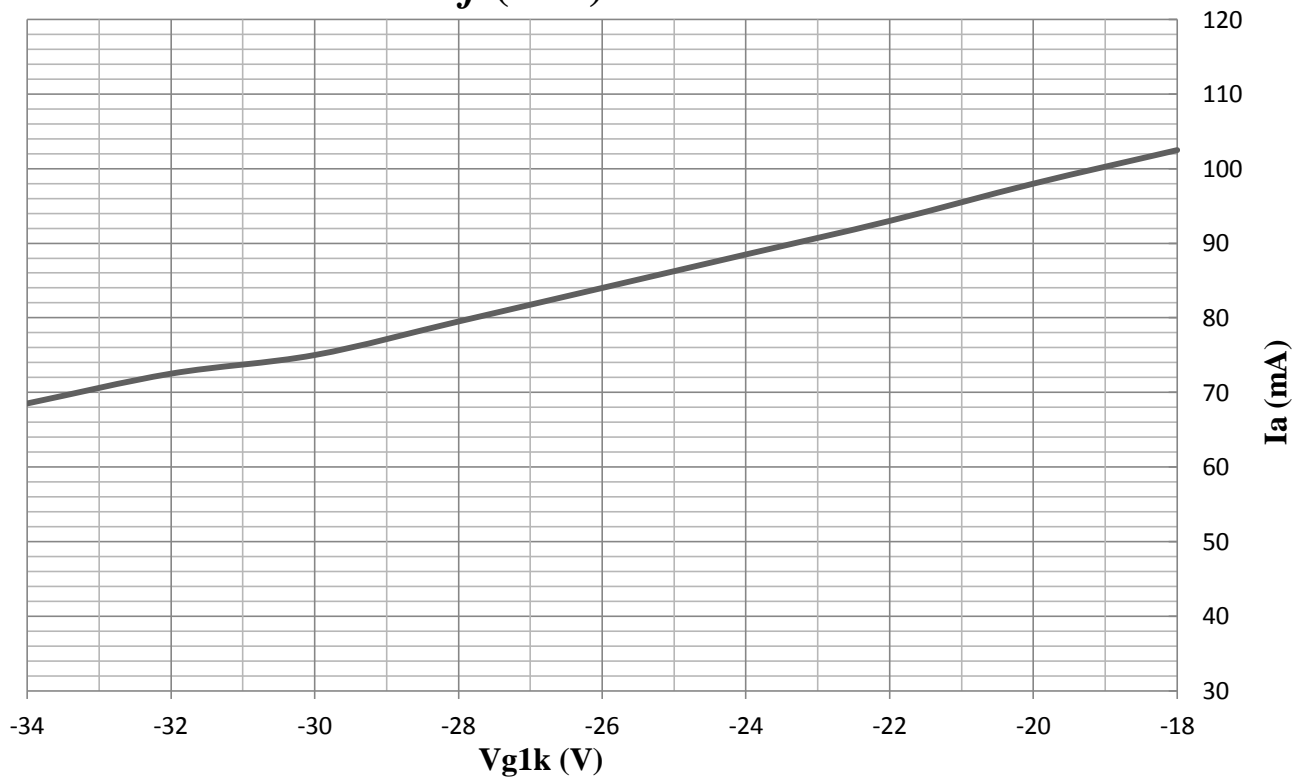


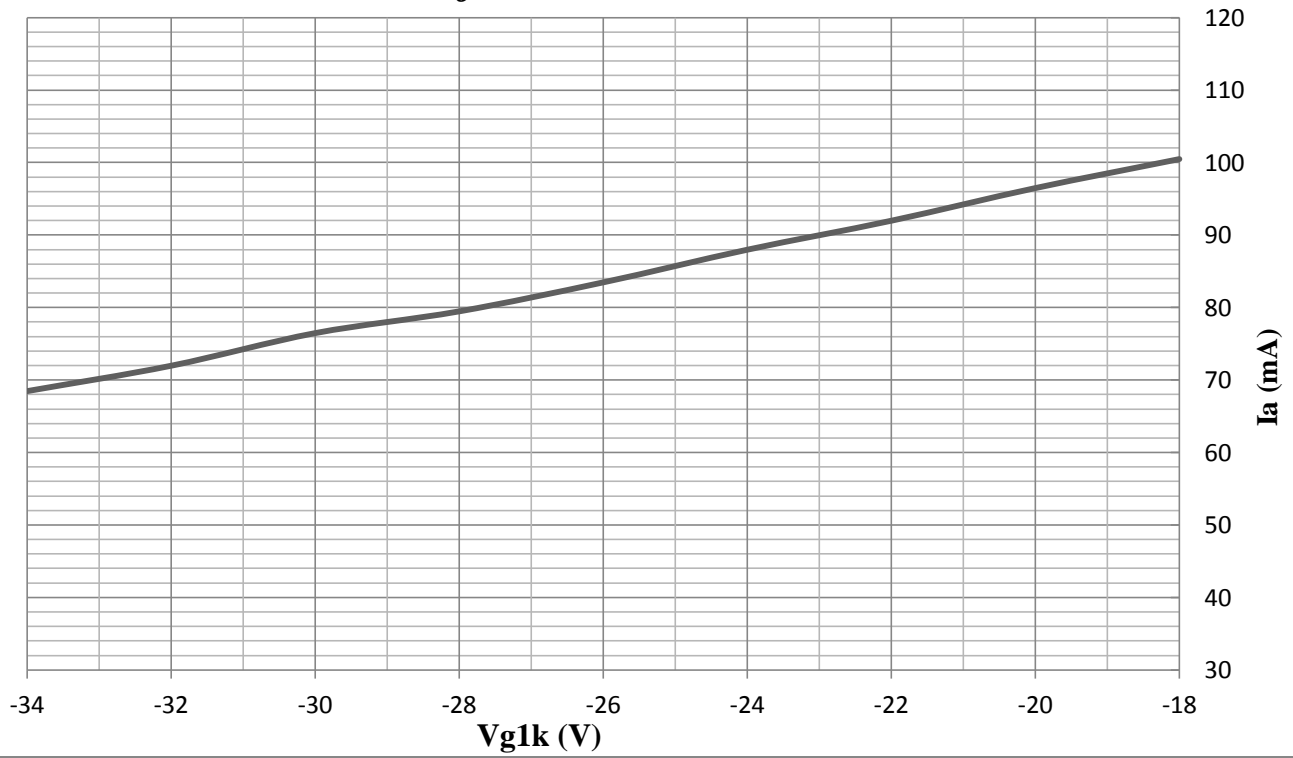
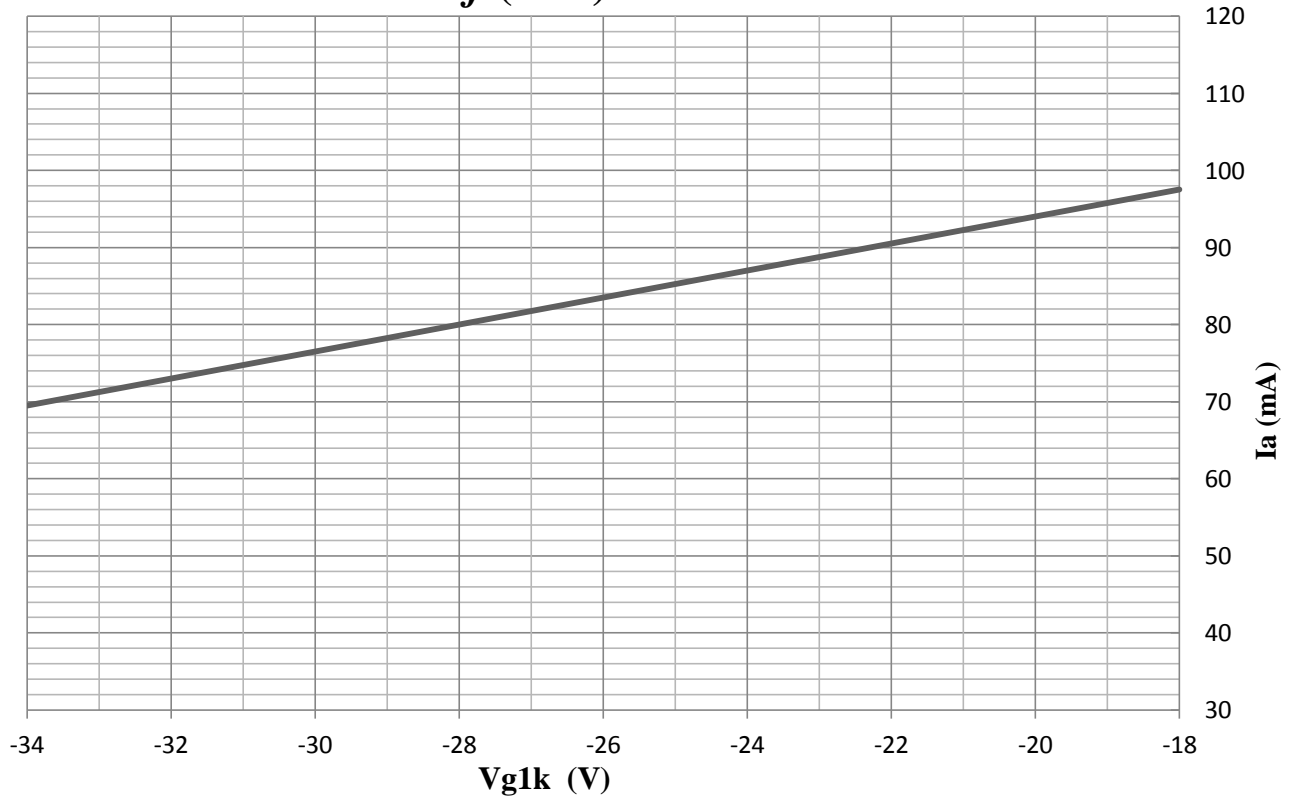
## APPENDIX F

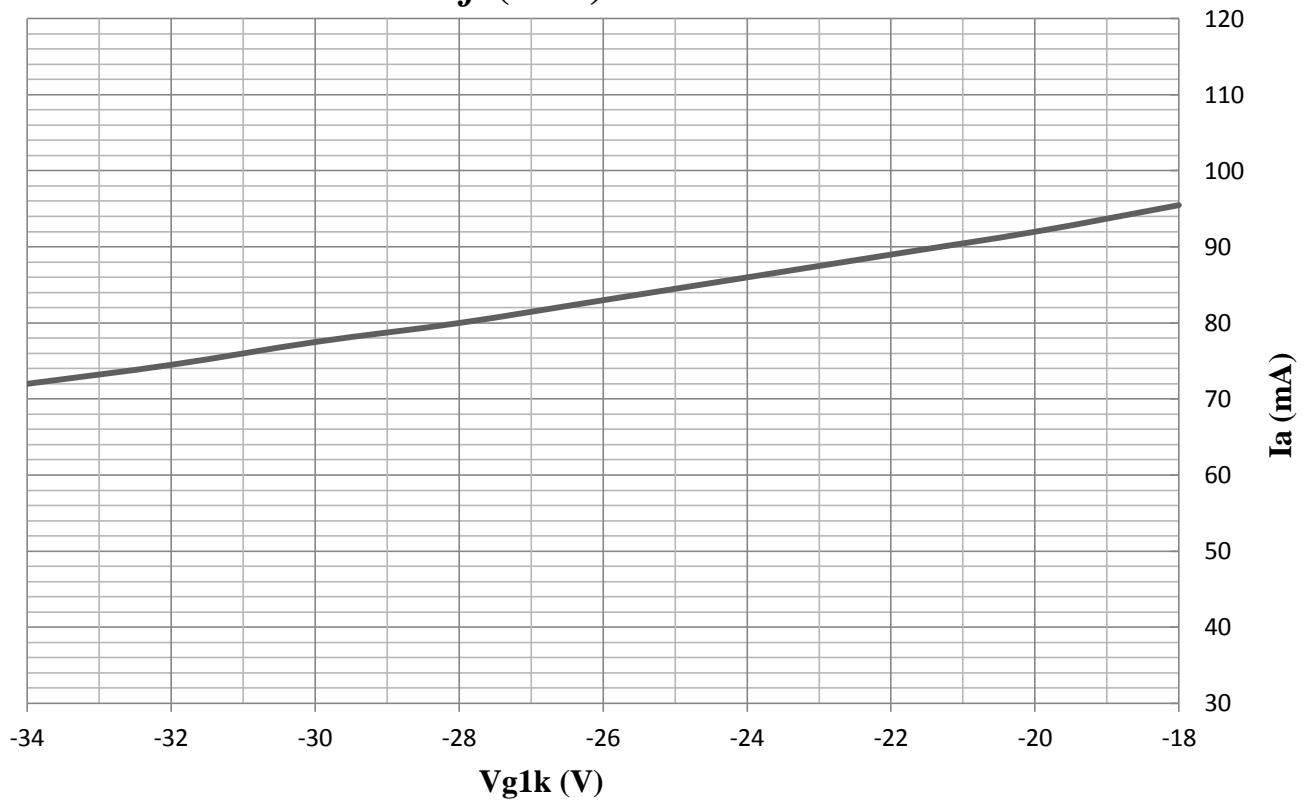
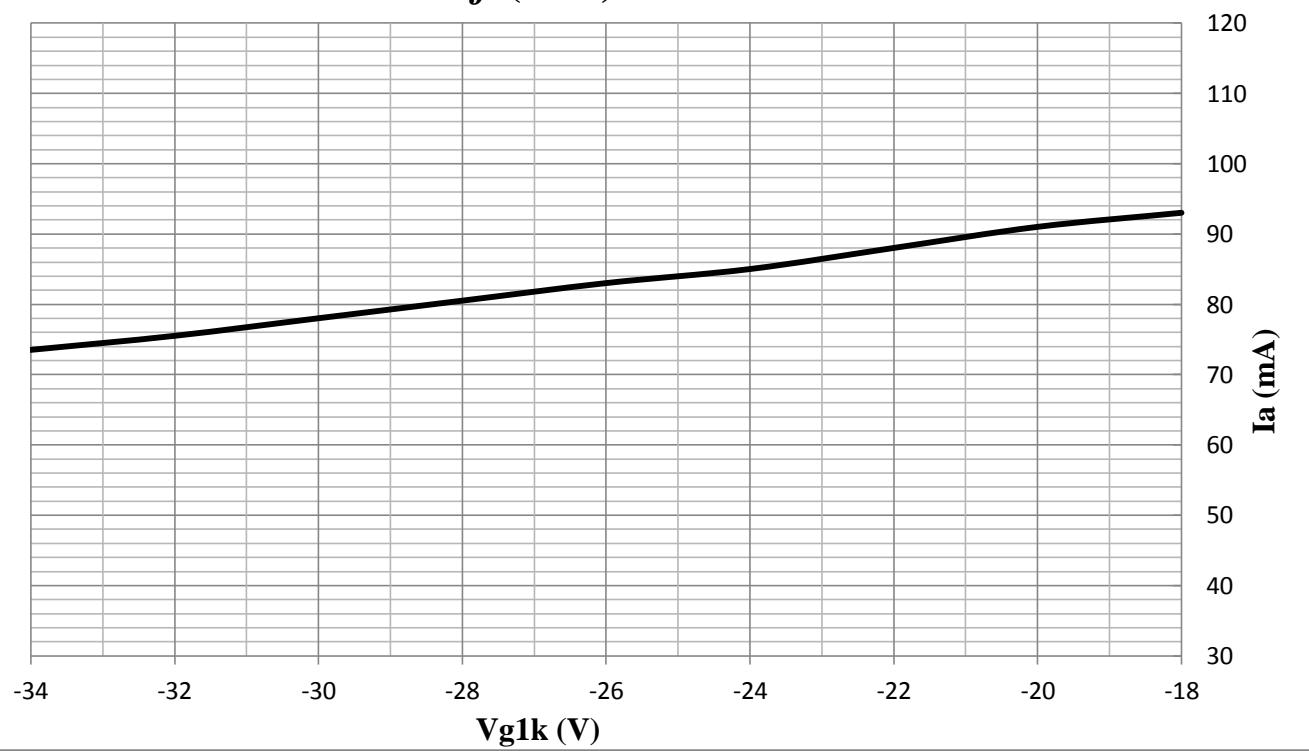
Constructed dynamic transconductance characteristics of KT88 for several screen grid tap.



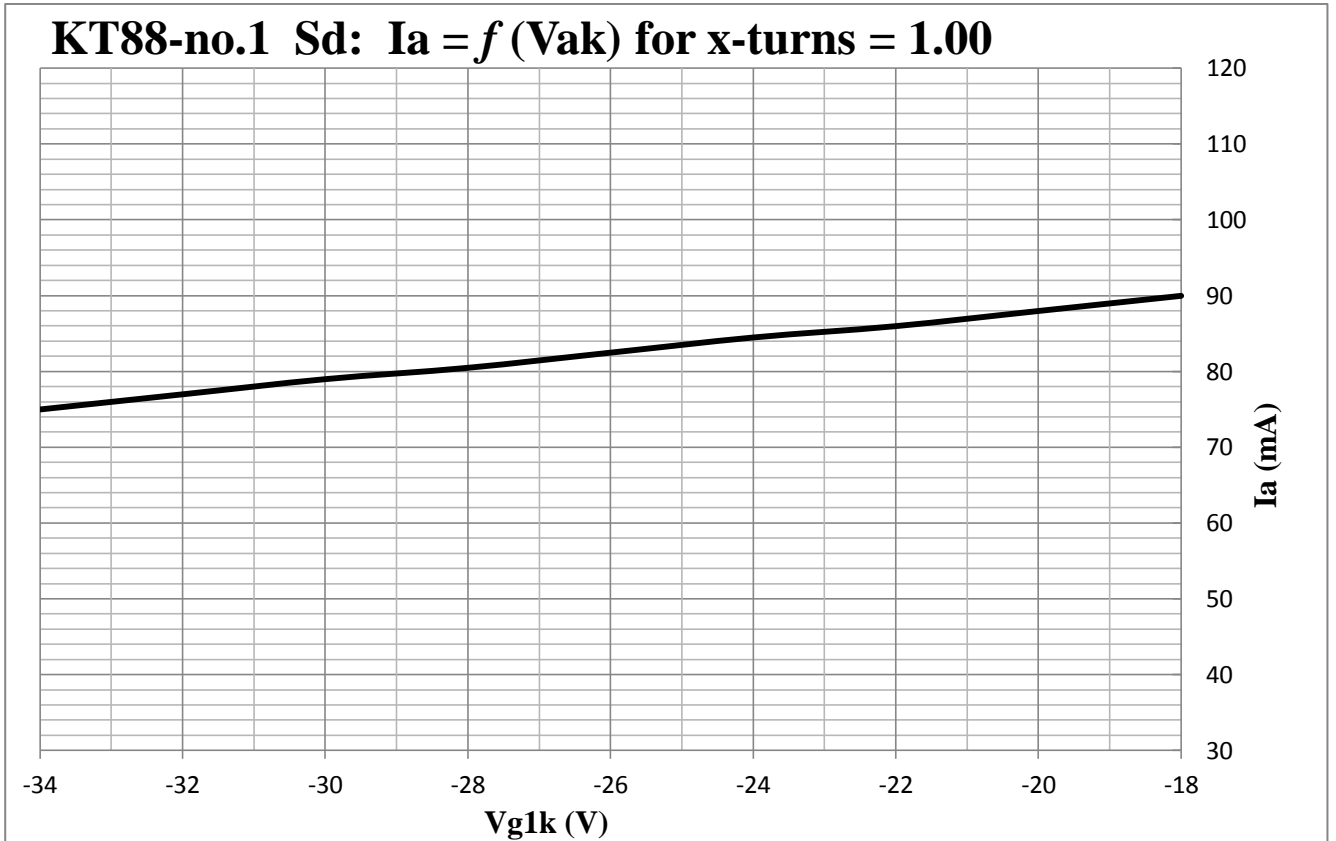
**KT88-no.1 Sd:  $I_a = f(V_{ak})$  for x-turns = 0.11****KT88-no.1 Sd:  $I_a = f(V_{ak})$  for x-turns = 0.17**

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